

# Study of the “low gain” background campaign


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# RUN 4 - The “low” vs “high” configurations

## Low Gain

- GEMs Voltages: 420 V
- Drift field: 500 V/cm
- Run Considered:
  - ➡ 55174 - 56883
  - ➡ ~ 1700 runs of bkg data
  - ➡ One daily calibration available



I used  $^{55}\text{Fe}$  data at step#3  
[i.e. center of LIME in z]  
to cross-calibrate the two  
sets of data

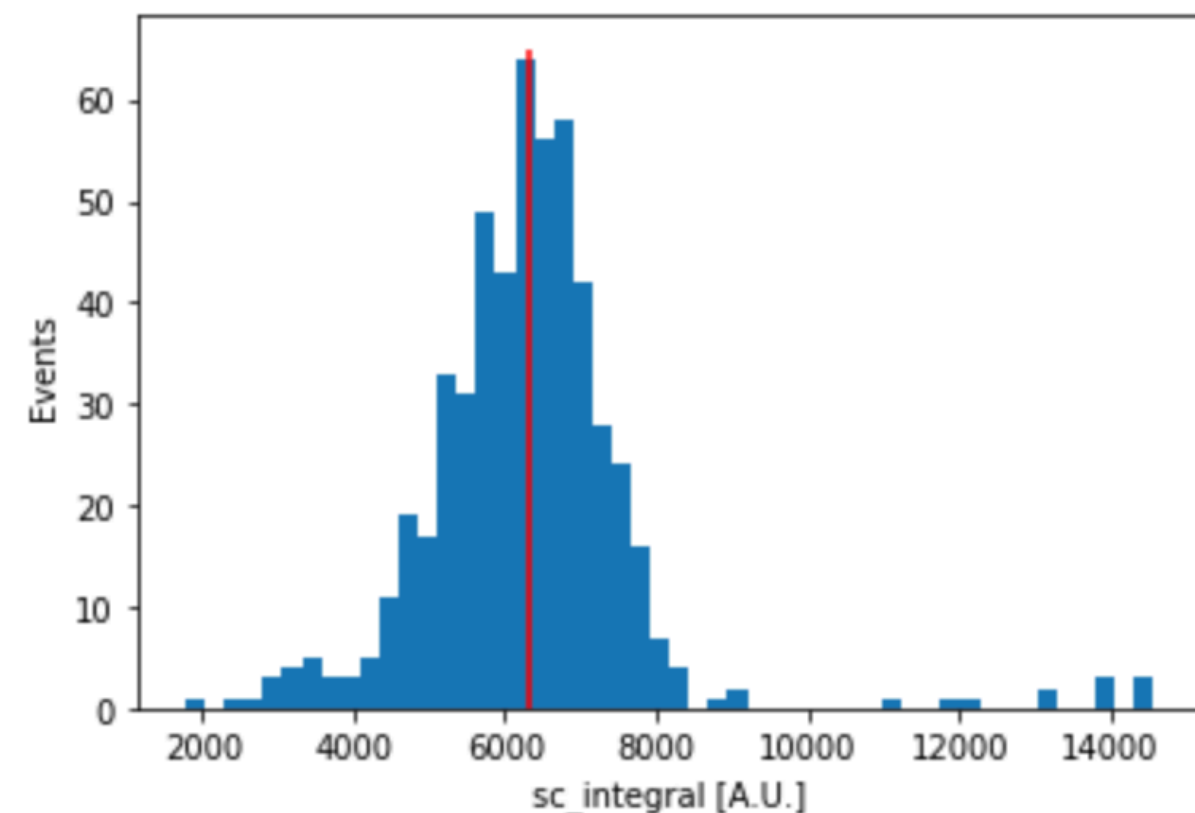
## High Gain

- GEMs Voltages: 440 V
- Drift field: 800 V/cm
- Run Considered:
  - ➡ 54505 - 55093
  - ➡ ~ 500 runs of bkg data
  - ➡ Chosen to be as **close** as possible **to low gain runs** to **reduce systematics** related to the detector conditions
  - ➡ Two daily calibrations available

# RUN 4 - The “low” vs “high” configurations

## Low Gain - $^{55}\text{Fe}$ calibration

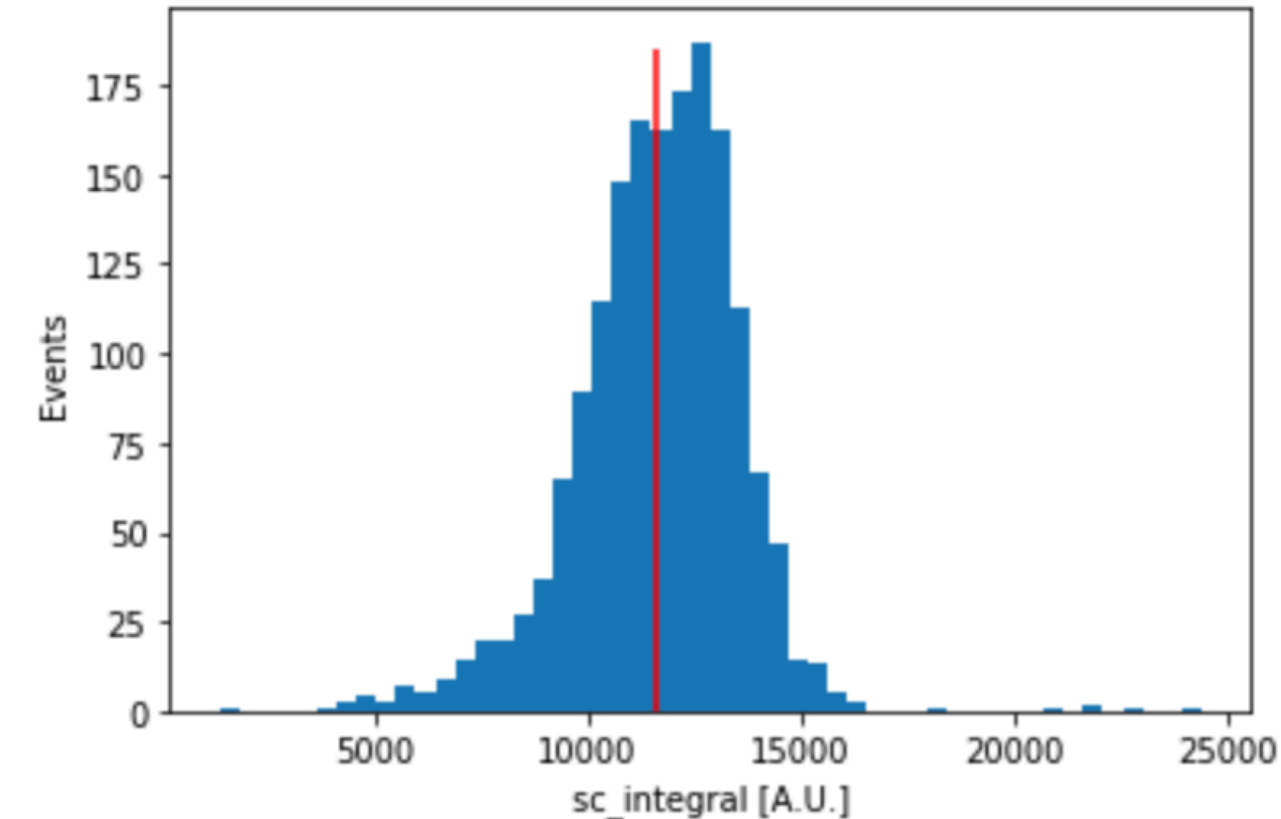
- Cuts to select for spot-like tracks
  - ➔  $\text{sc\_rms} > 6$  [fake clusters] \*
  - ➔  $\text{sc\_tgausssigma} > 0.5 / 0.152$  [events on the CMOS]
  - ➔  $R < 800$  px [fiducialization]
  - ➔  $\text{sc\_width}/\text{sc\_length} > 0.8$  [round tracks]
  - ➔  $\text{sc\_integral} < 15'000$



LY (5.9 keV) =  $6311 \pm 63$

## High Gain - $^{55}\text{Fe}$ calibration

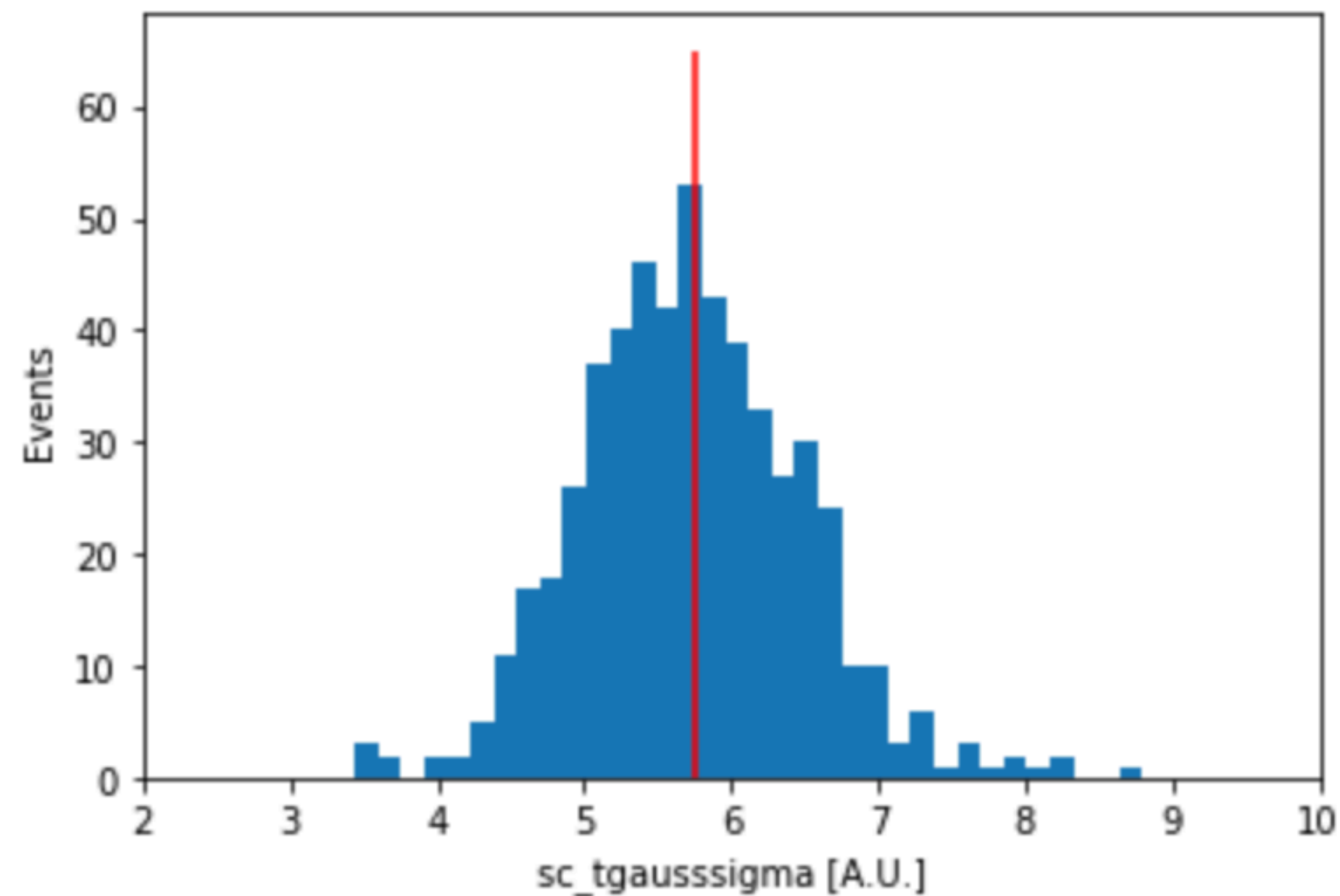
- Cuts to select for spot-like tracks
  - ➔  $\text{sc\_rms} > 6$  [fake clusters] \*
  - ➔  $\text{sc\_tgausssigma} > 0.5 / 0.152$  [events on the CMOS]
  - ➔  $R < 800$  px [fiducialization]
  - ➔  $\text{sc\_width}/\text{sc\_length} > 0.8$  [round tracks]
  - ➔  $\text{sc\_integral} < 25'000$



LY (5.9 keV) =  $11641 \pm 48$

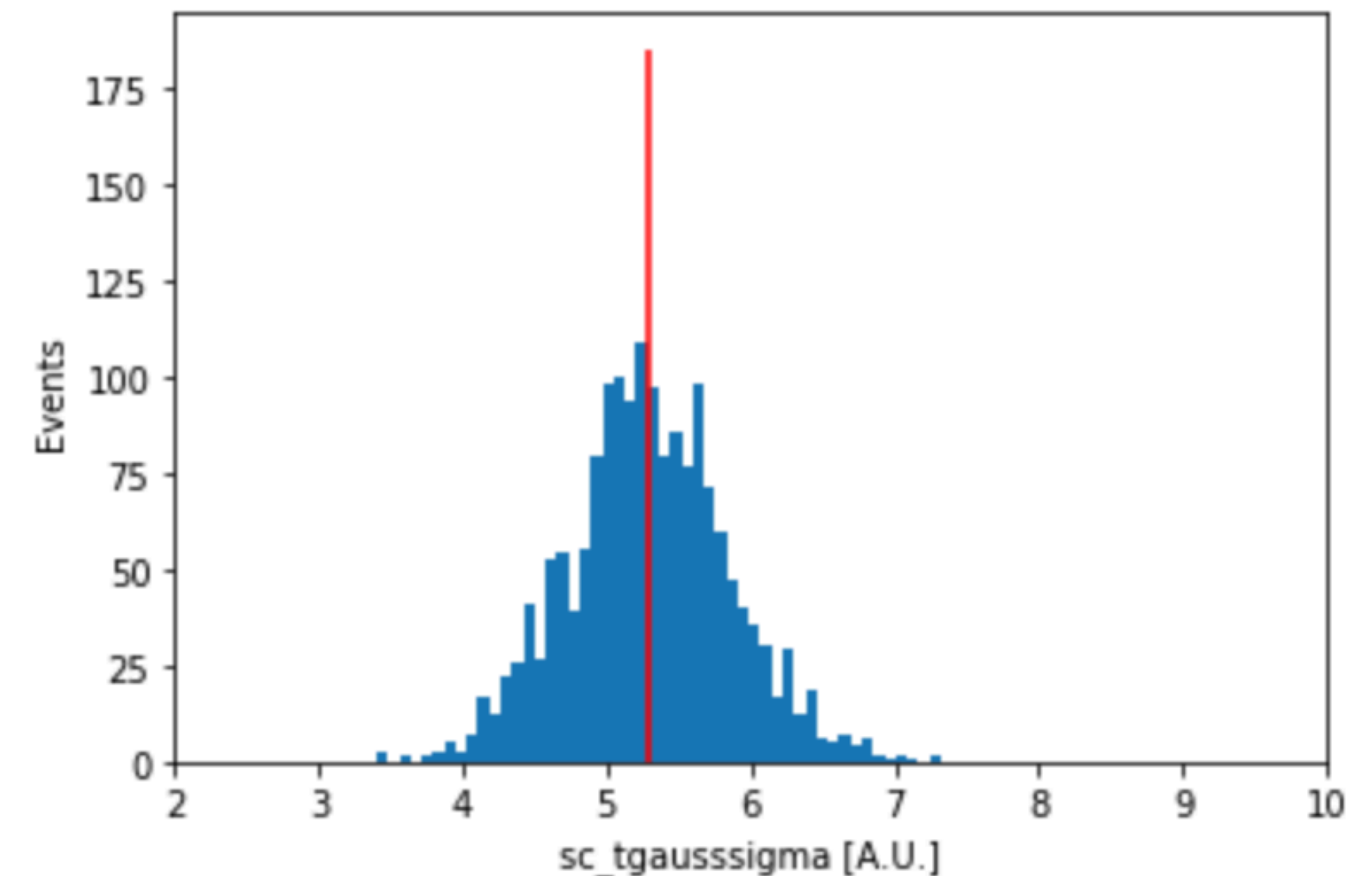
# RUN 4 - The “low” vs “high” configurations

## Low Gain - Fe diffusion



$$\text{sc\_tgausssigma} = 5.747 \pm 0.035$$

## High Gain - Fe diffusion

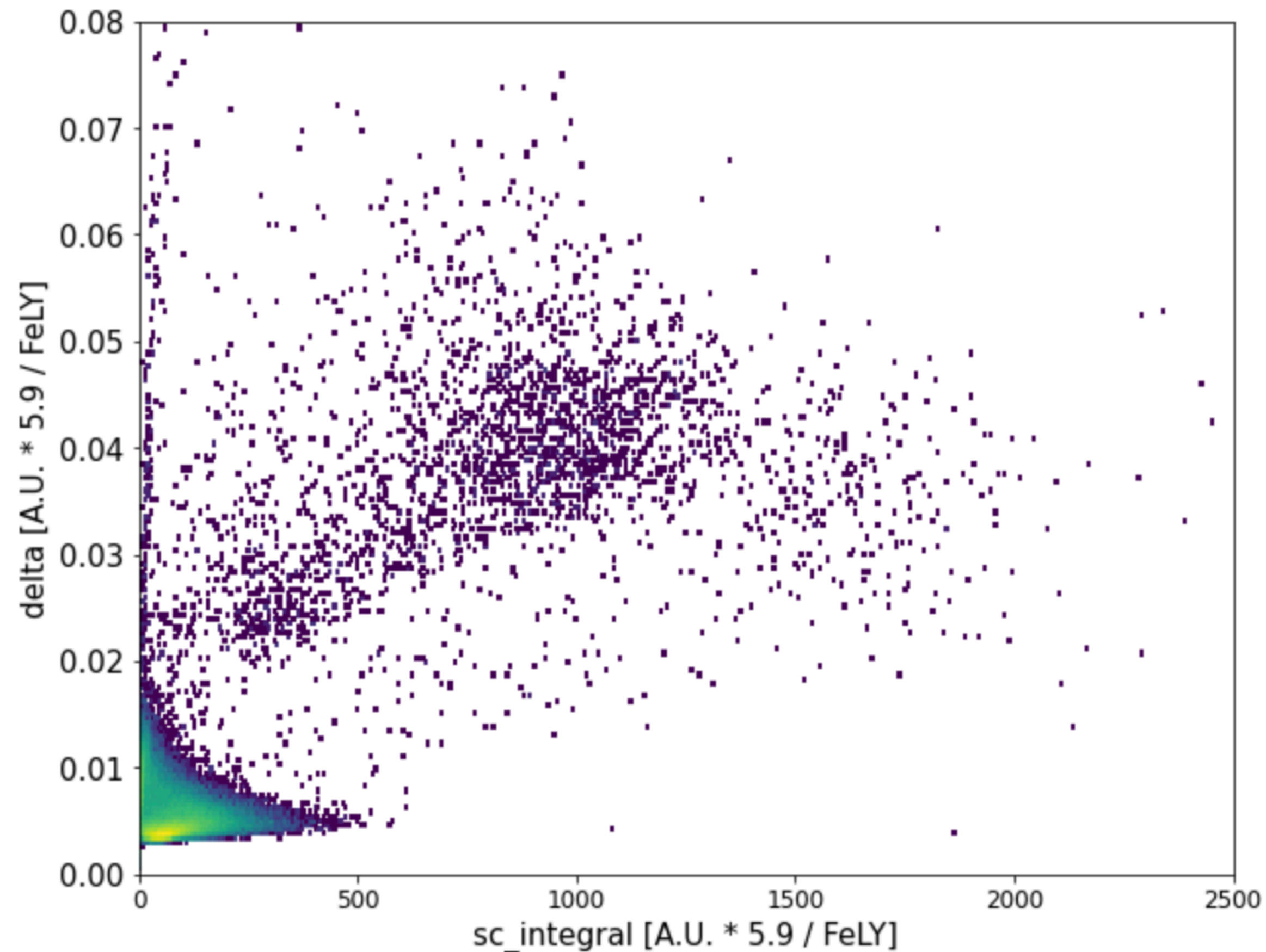


$$\text{sc\_tgausssigma} = 5.292 \pm 0.014$$

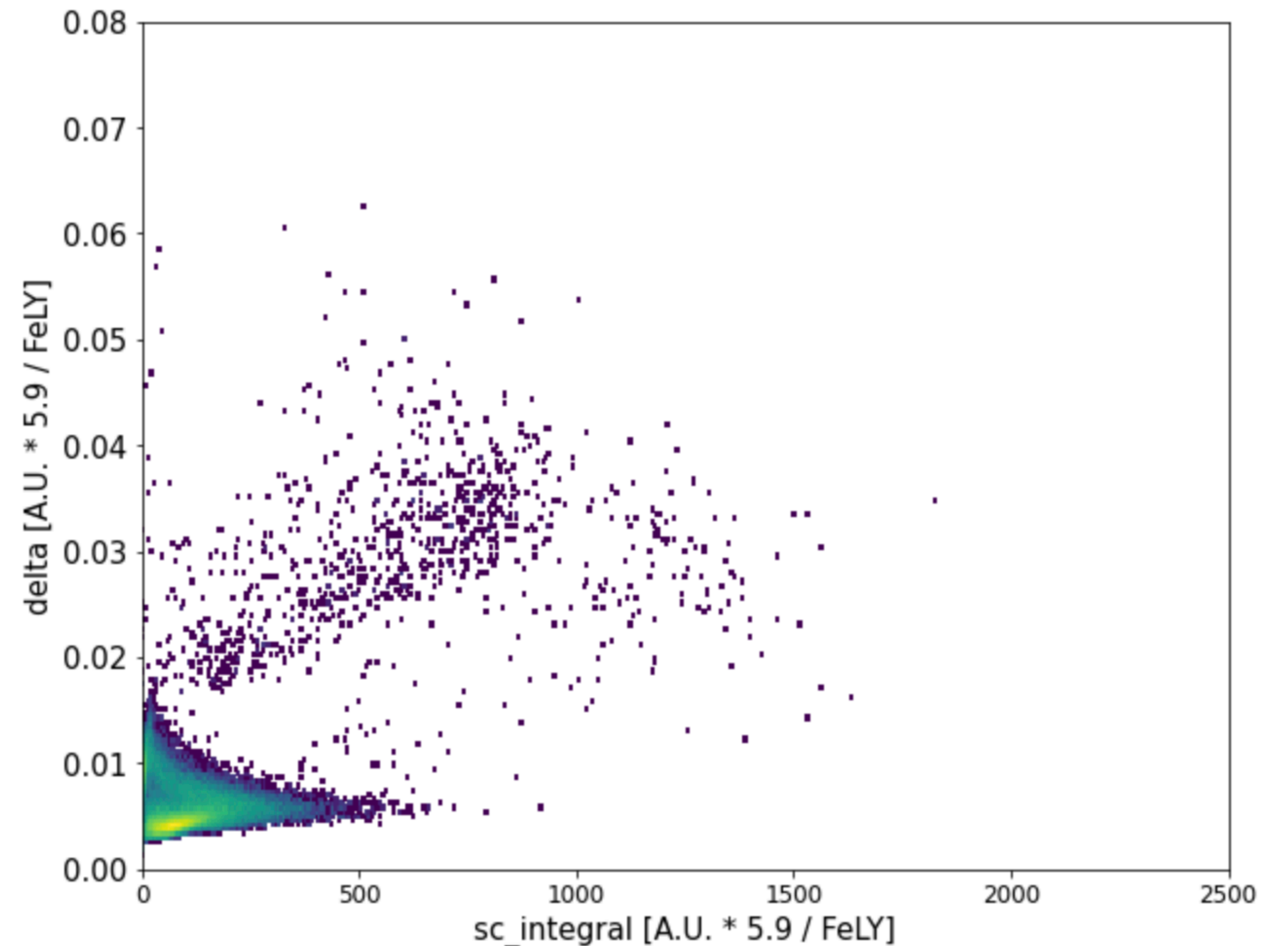


# RUN 4 - The “low” vs “high” configurations

Low Gain - High Energy spectra



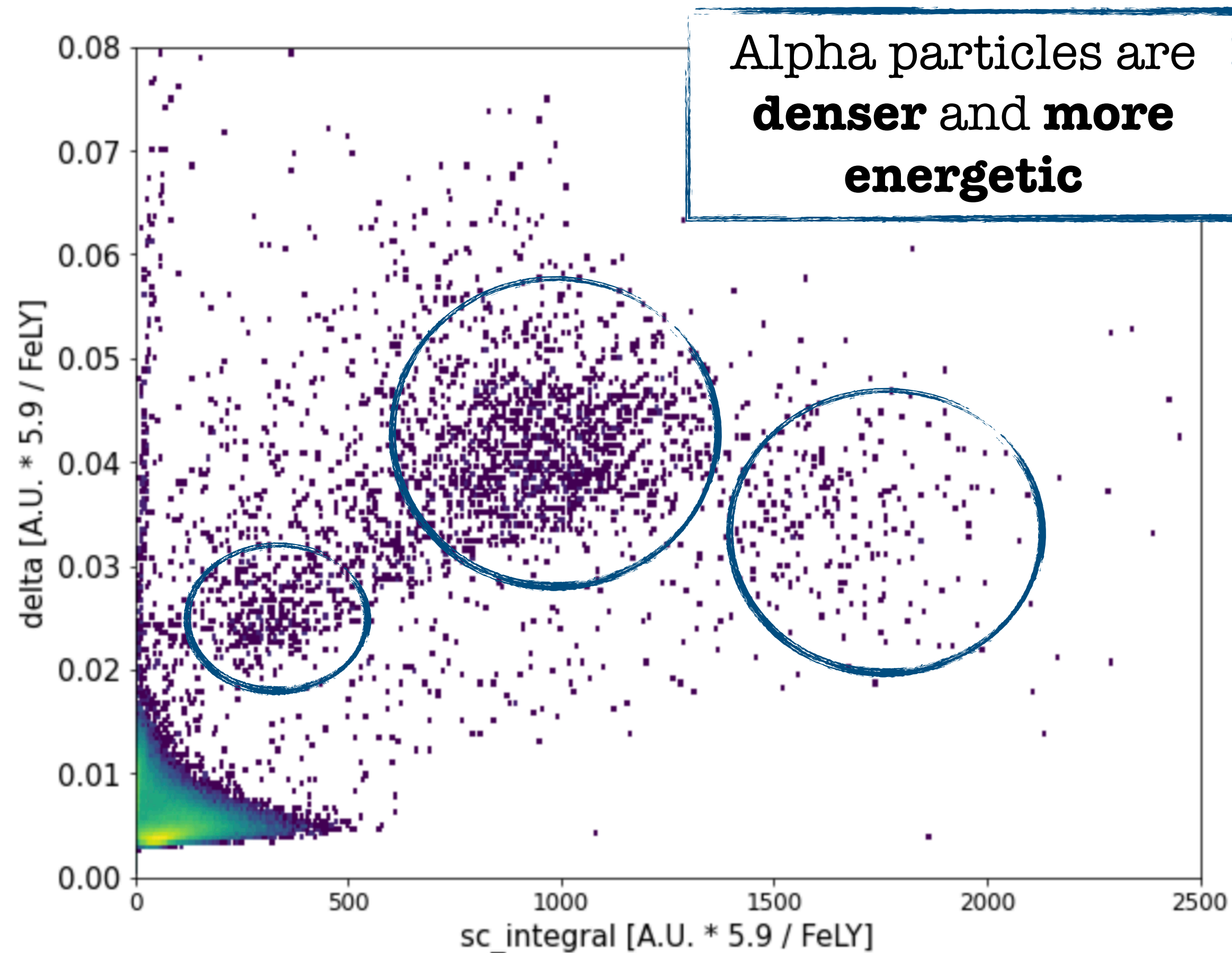
High Gain - High Energy spectra



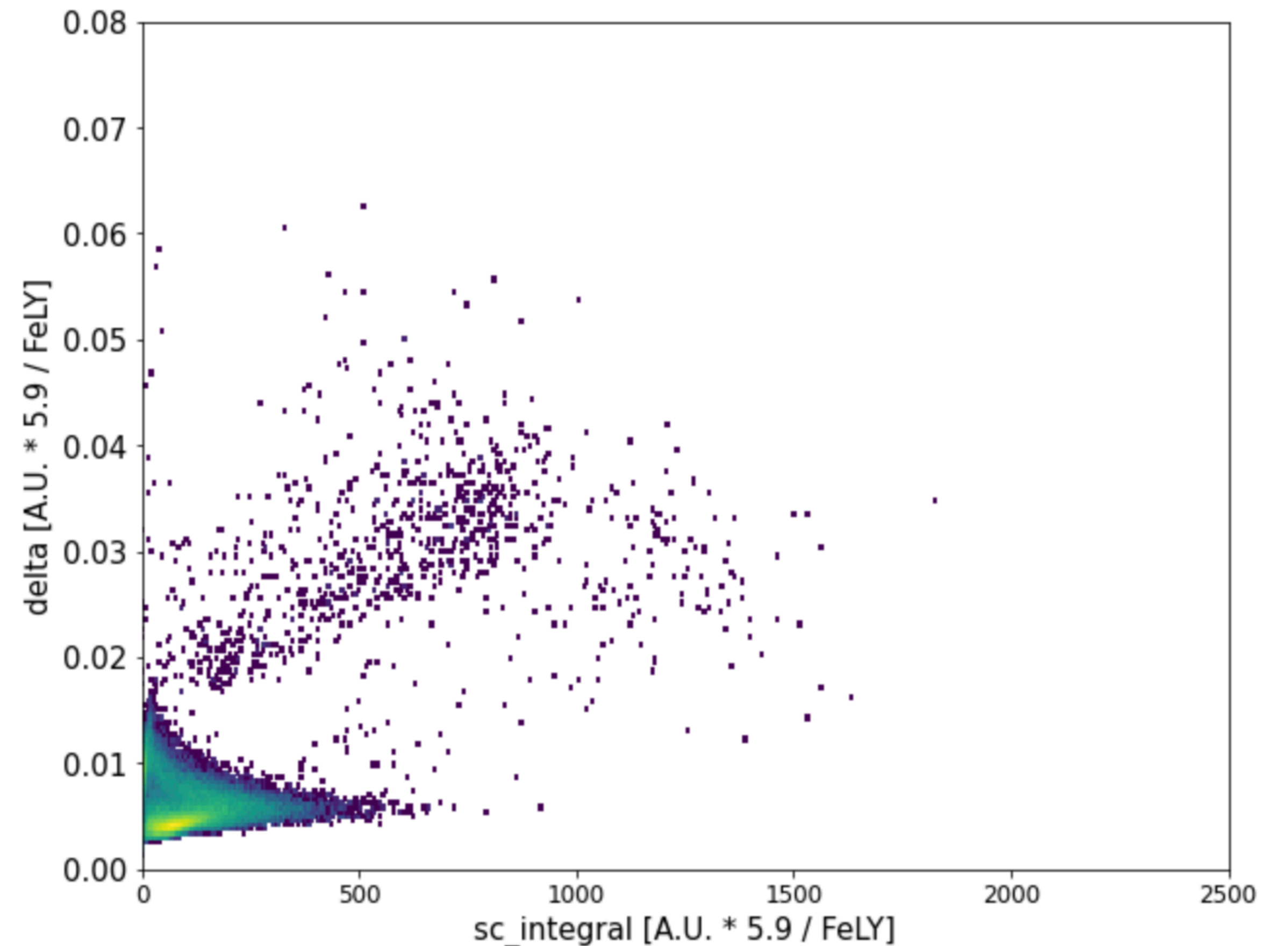
N.B. here there's a 3x in statistics

# RUN 4 - The “low” vs “high” configurations

## Low Gain - High Energy spectra



## High Gain - High Energy spectra

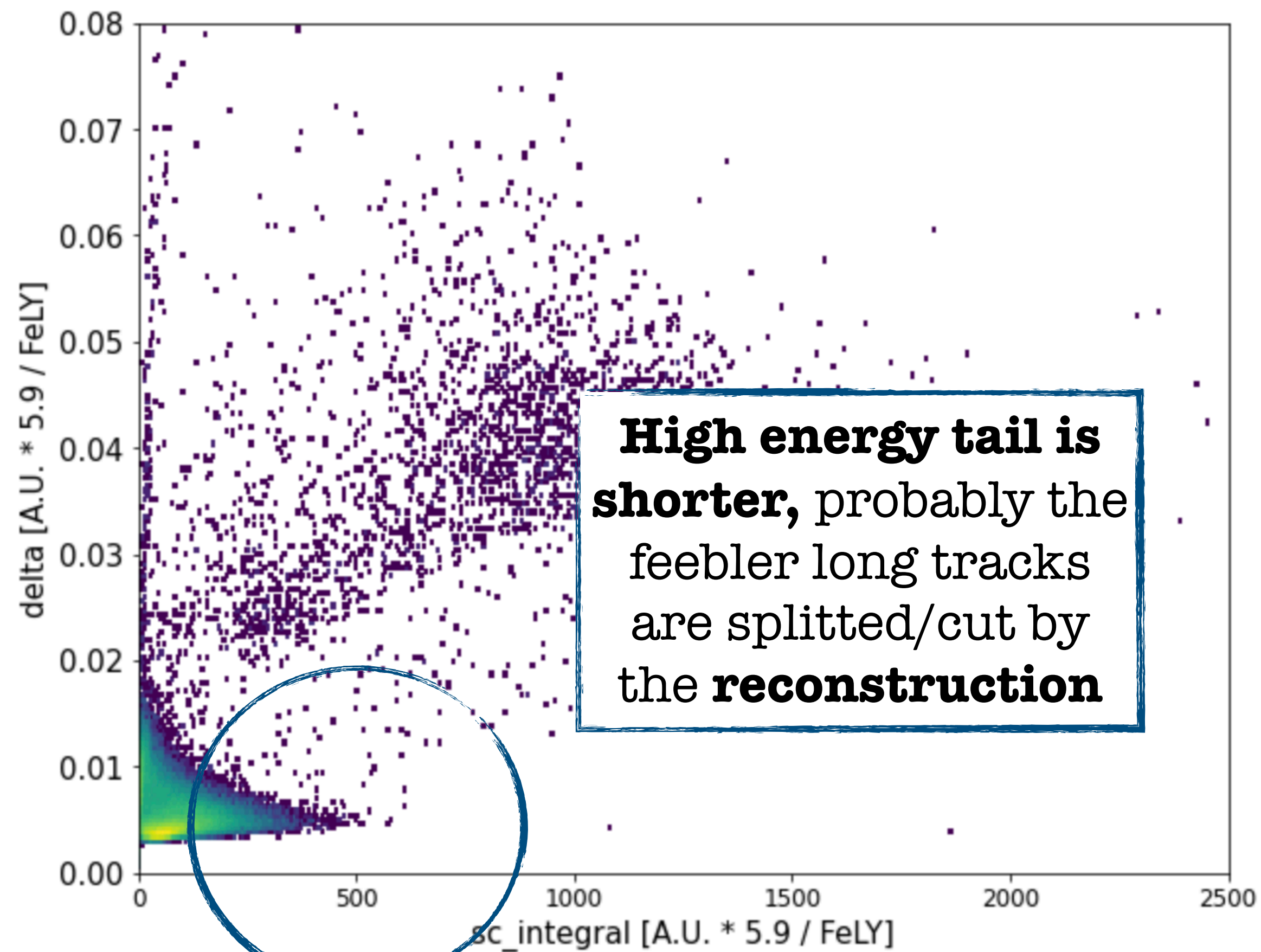


N.B. here there's a 3x in statistics



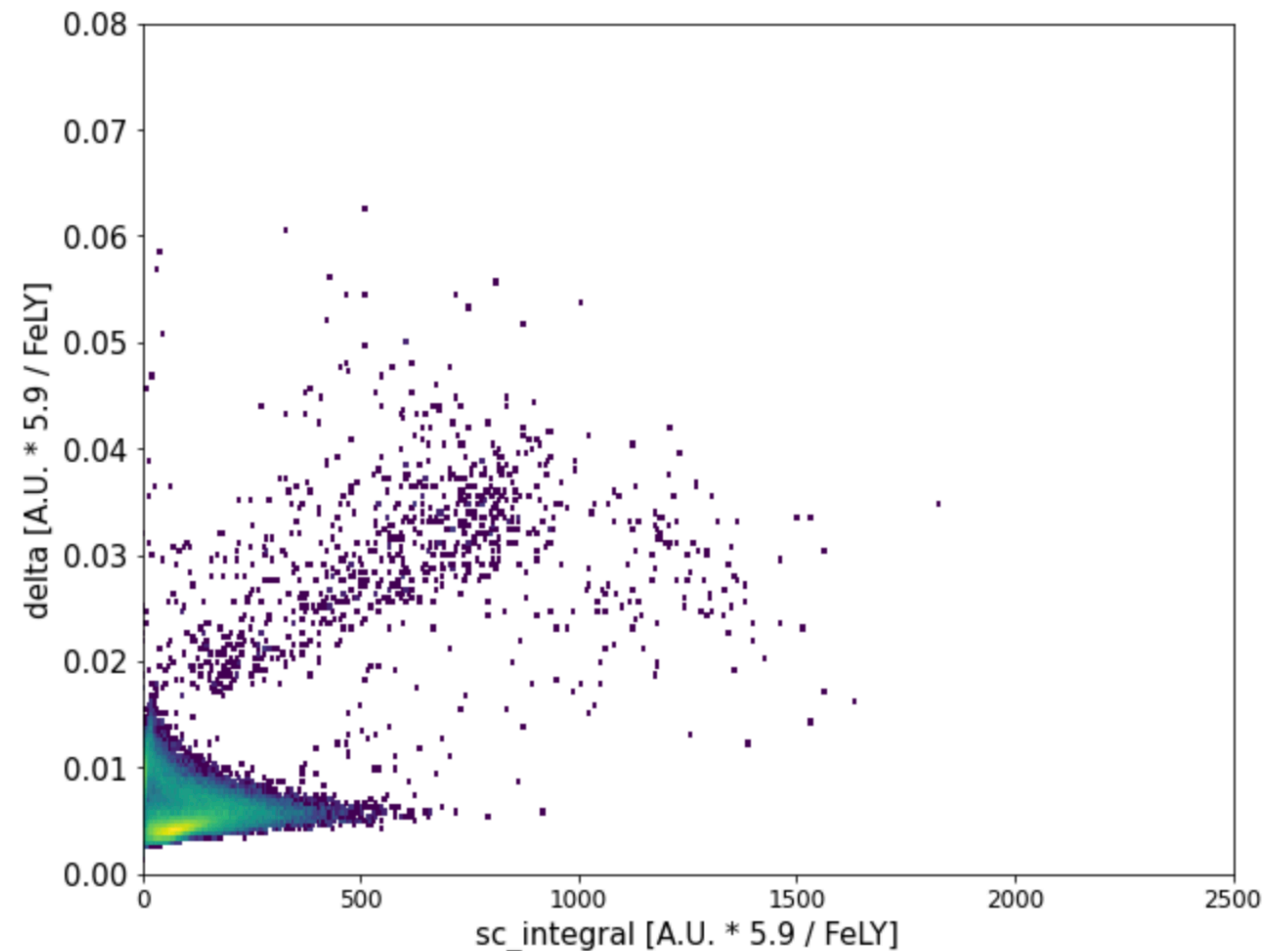
# RUN 4 - The “low” vs “high” configurations

## Low Gain - High Energy spectra



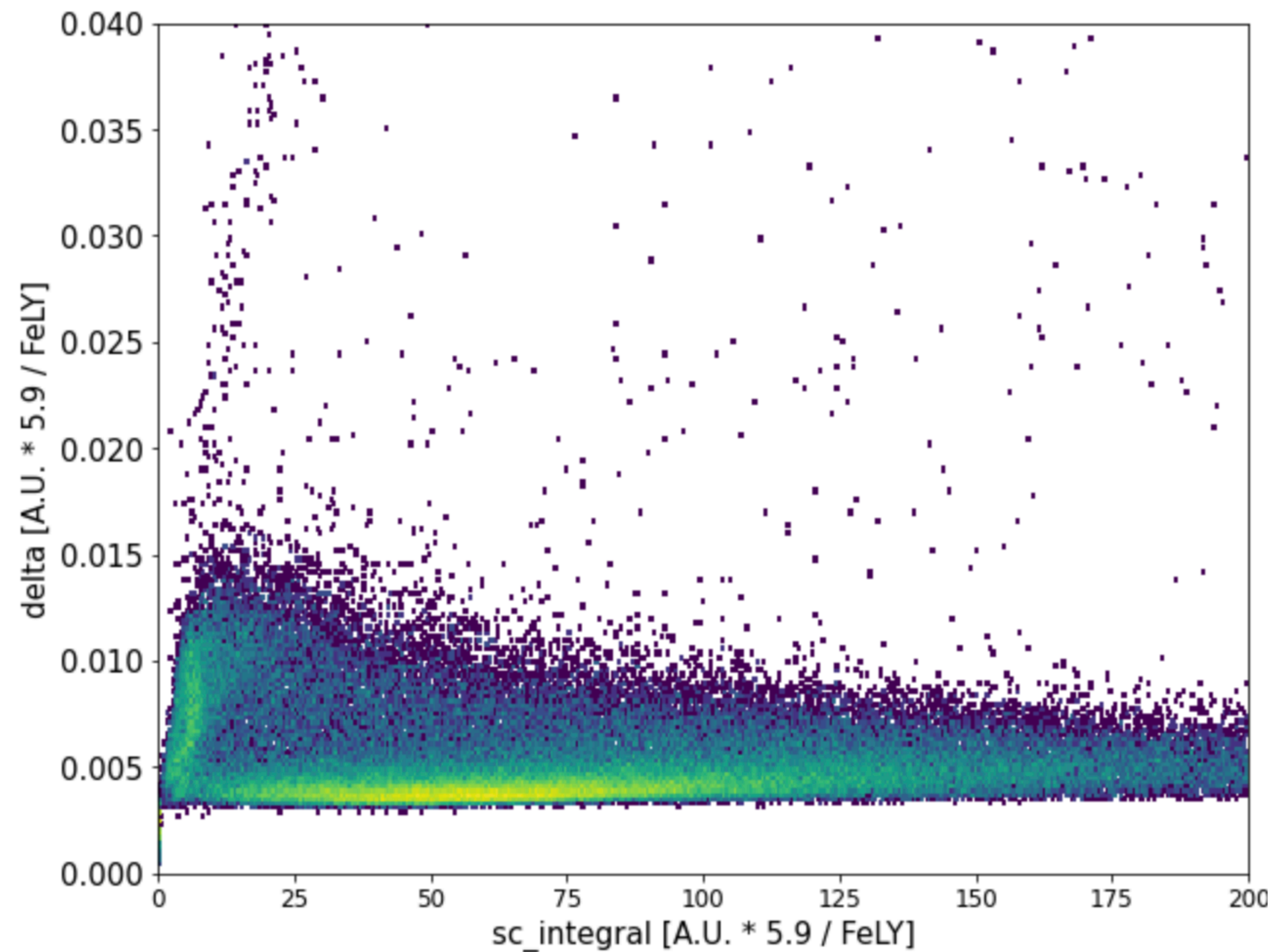
N.B. here there's a 3x in statistics

## High Gain - High Energy spectra

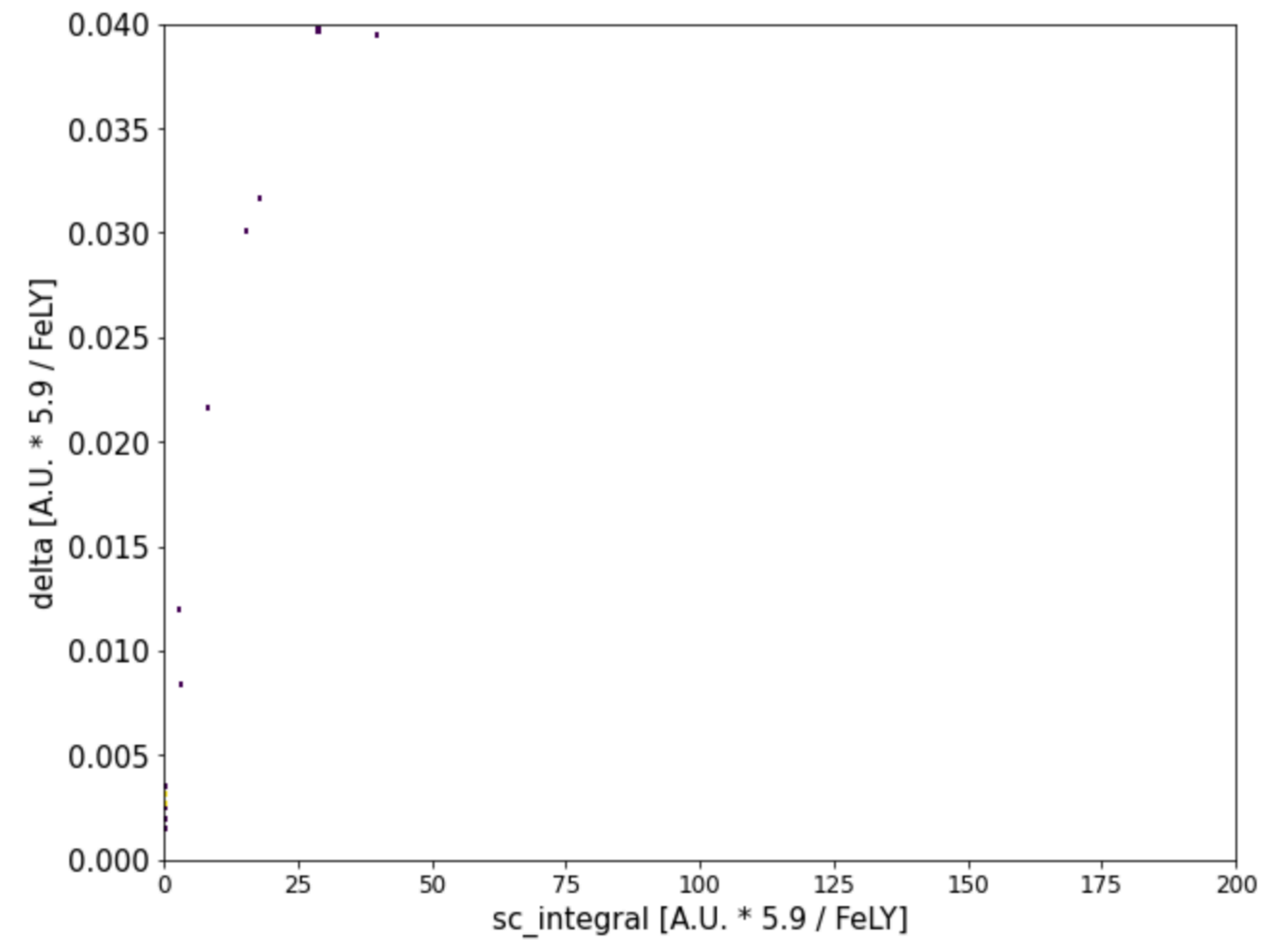


# RUN 4 - The “low” vs “high” configurations

## Low Gain - Low Energy spectra



## Low Gain - Low Energy spectra Pedestals

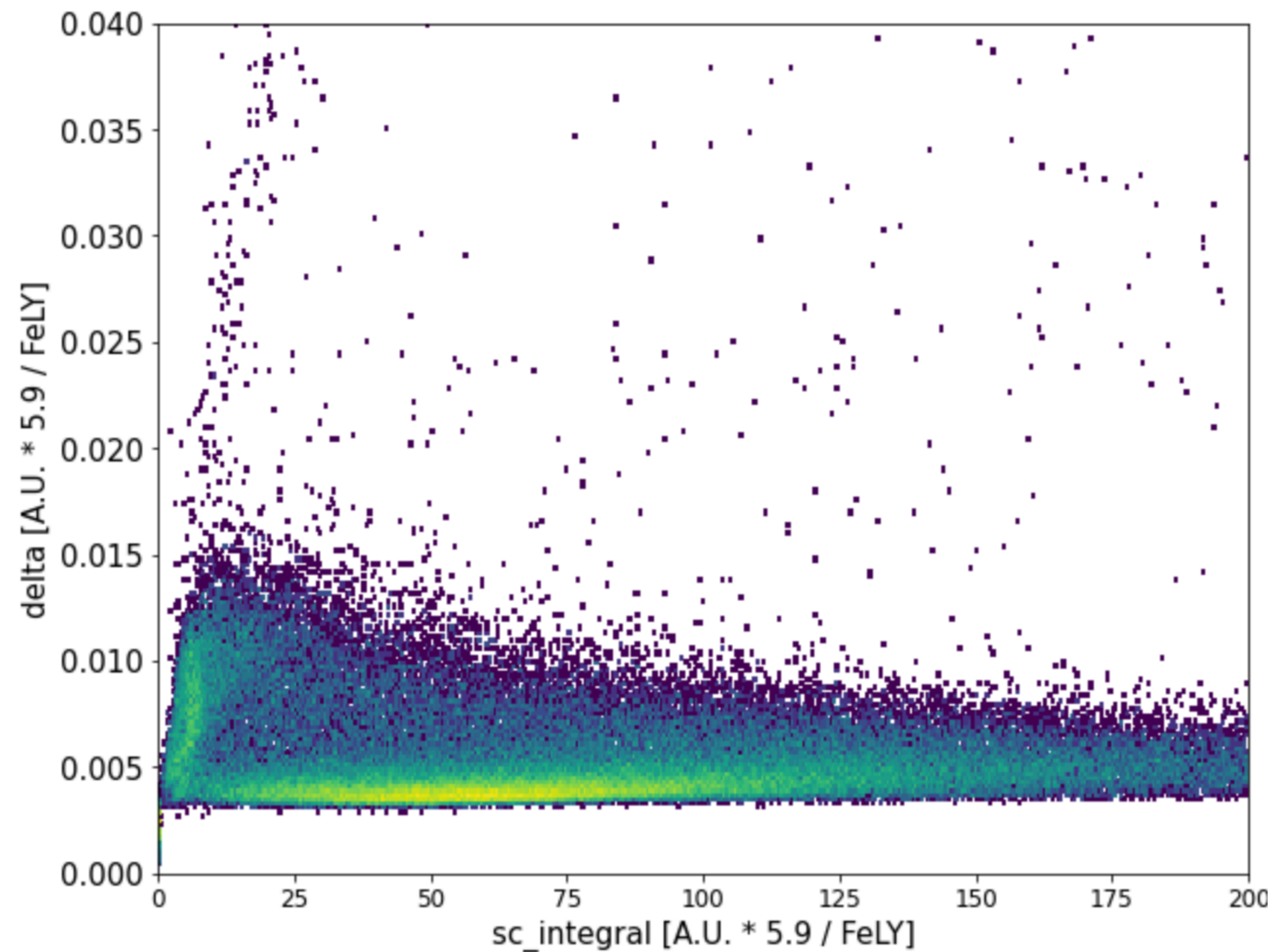


N.B. here statistics is much lower

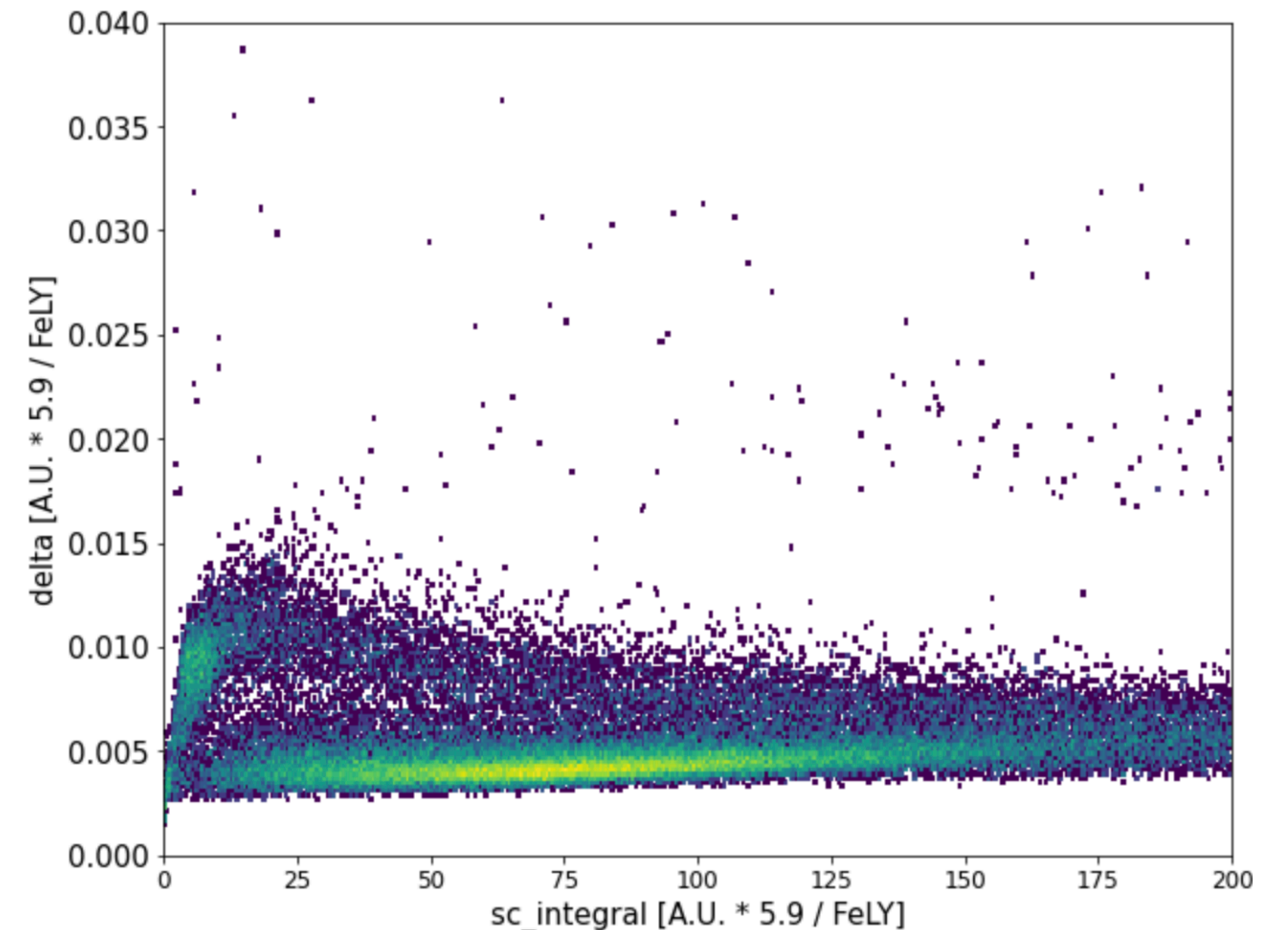


# RUN 4 - The “low” vs “high” configurations

Low Gain - Low Energy spectra



High Gain - Low Energy spectra

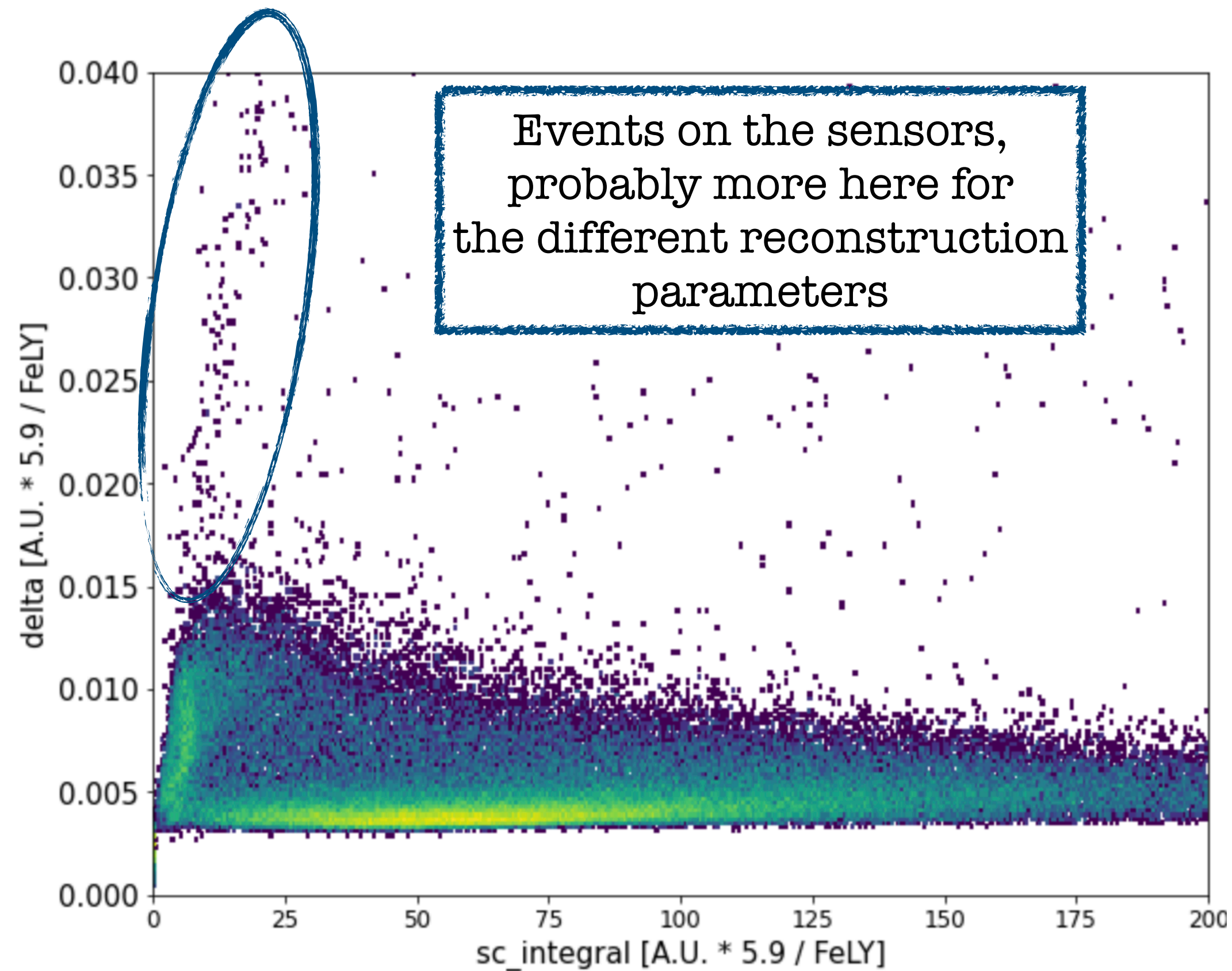


N.B. here there's a 3x in statistics

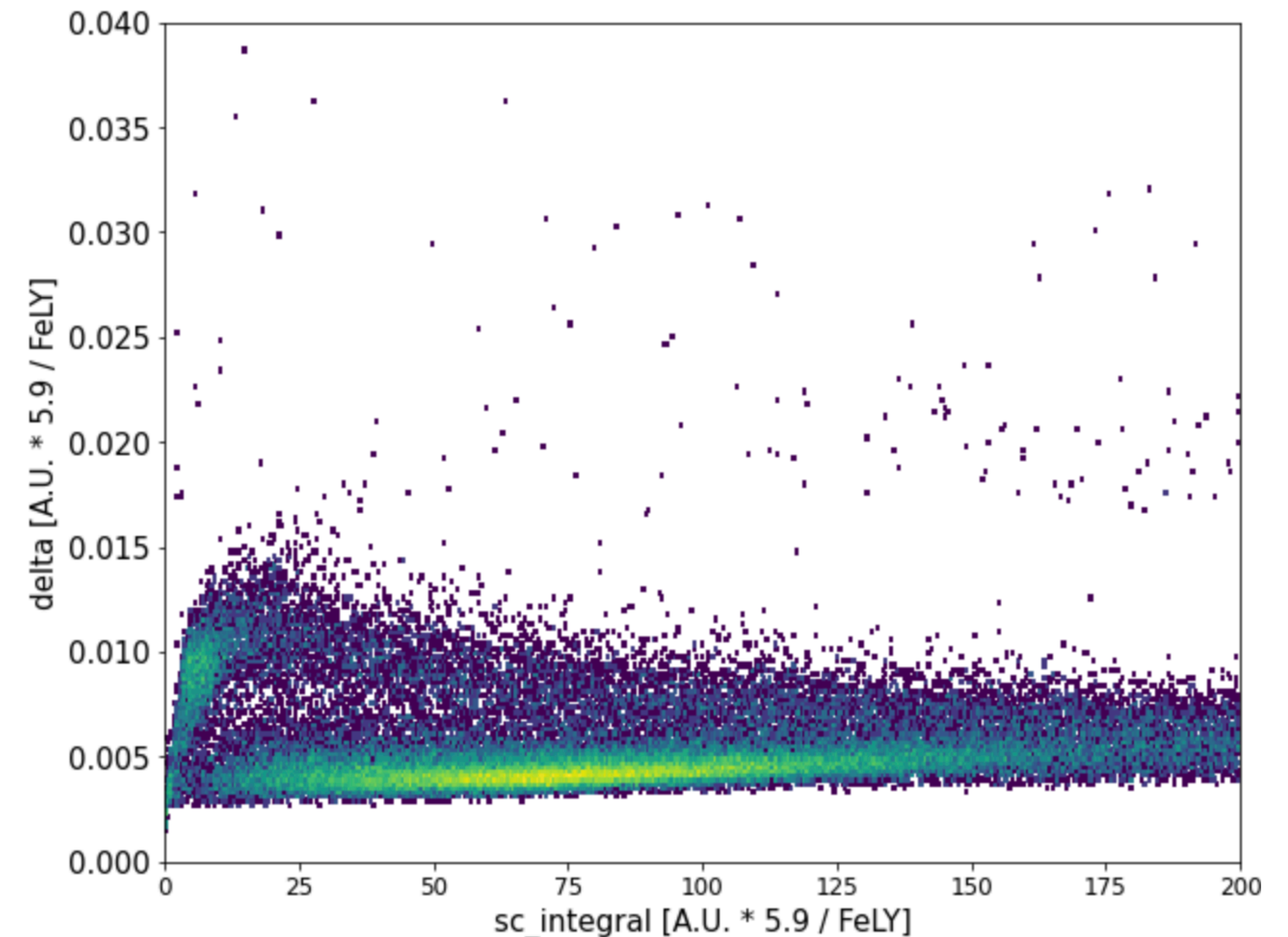


# RUN 4 - The “low” vs “high” configurations

## Low Gain - Low Energy spectra



## High Gain - Low Energy spectra

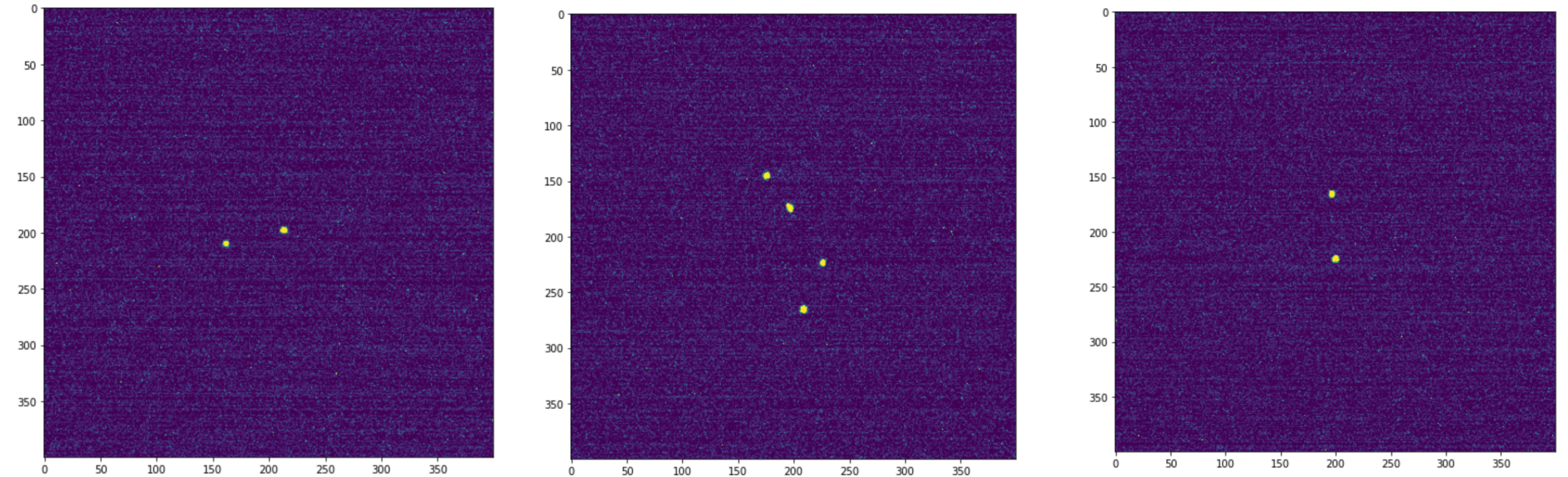
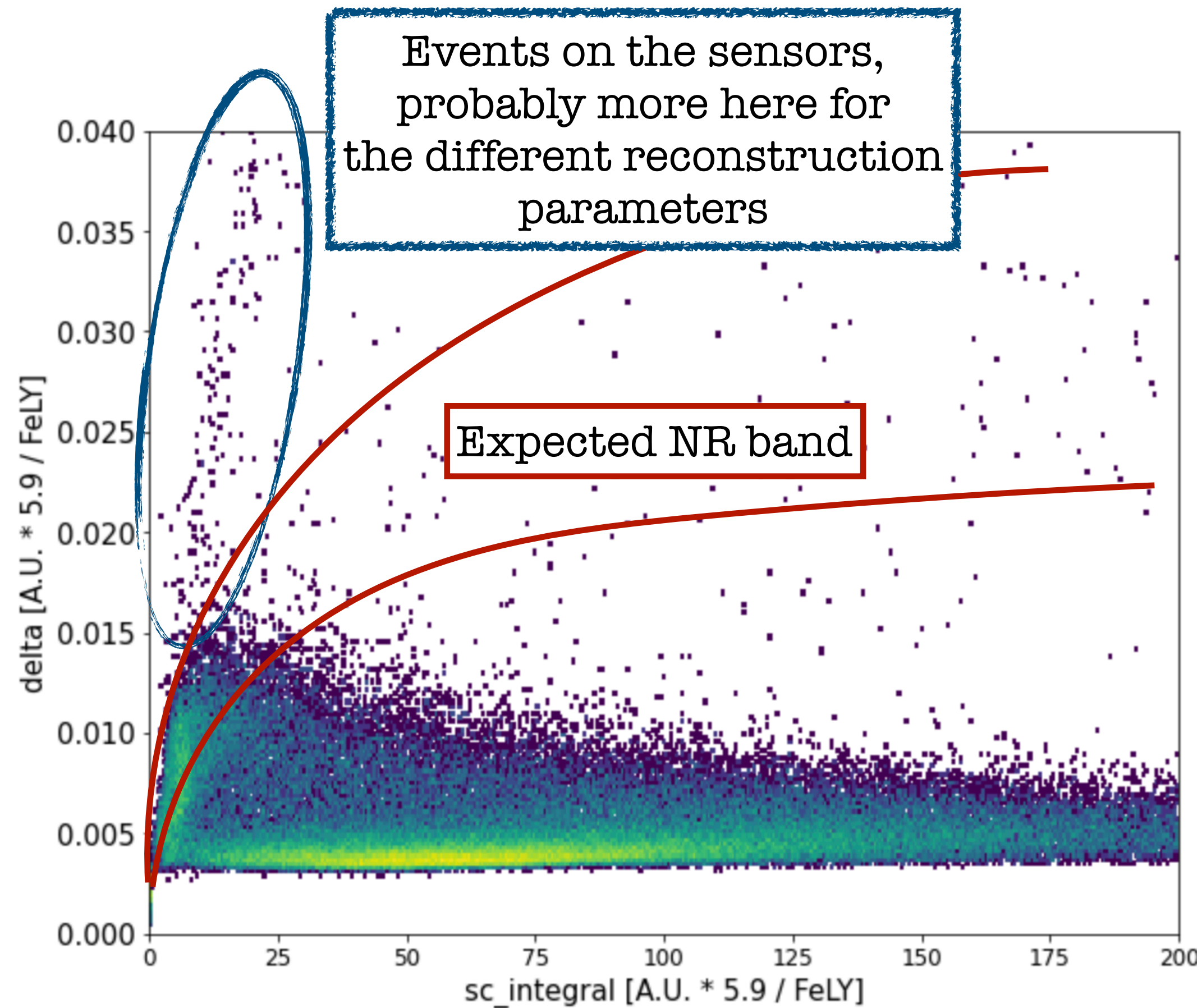


N.B. here there's a 3x in statistics



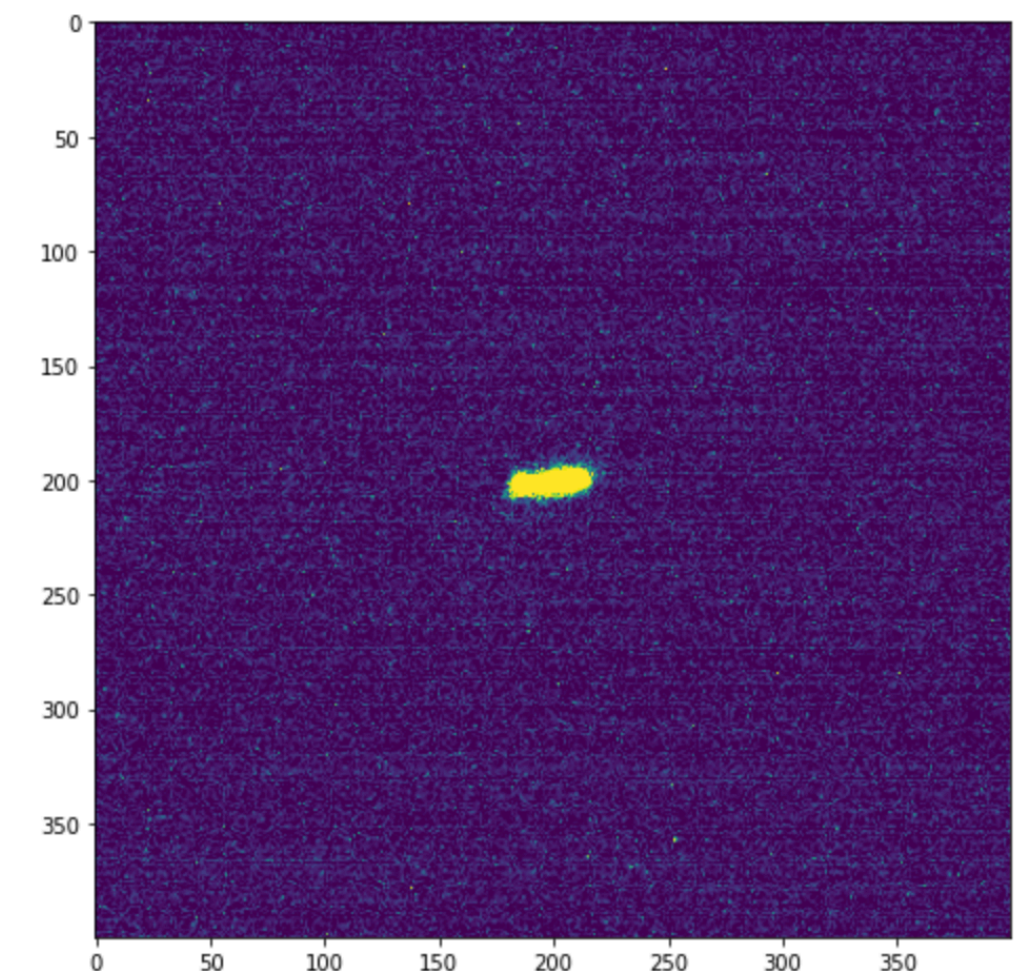
# RUN 4 - The “low” vs “high” configurations

## Low Gain - Low Energy spectra



Mostly multiple hits on the CMOS clustered as a single track. How to remove them without removing interesting NR events?

Just for comparison, how a NR deposit looks like: [same pixel range]



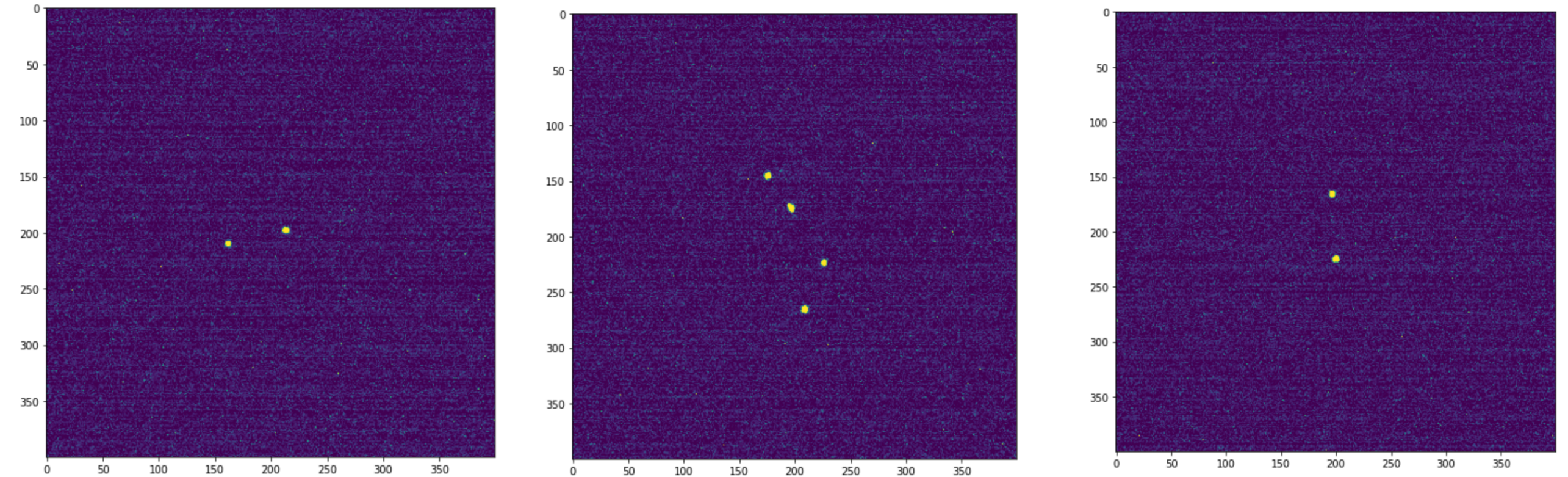


# RUN 4 - The “low” vs “high” configurations

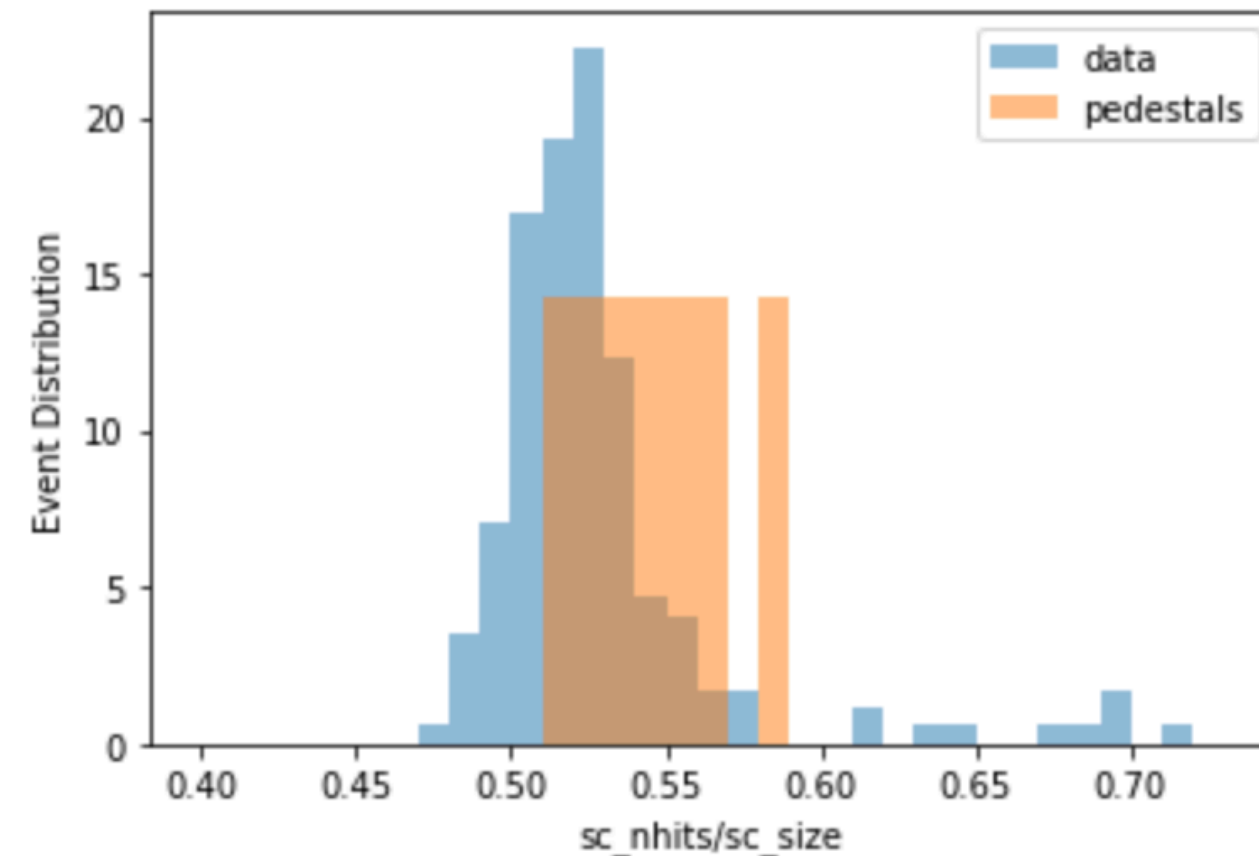
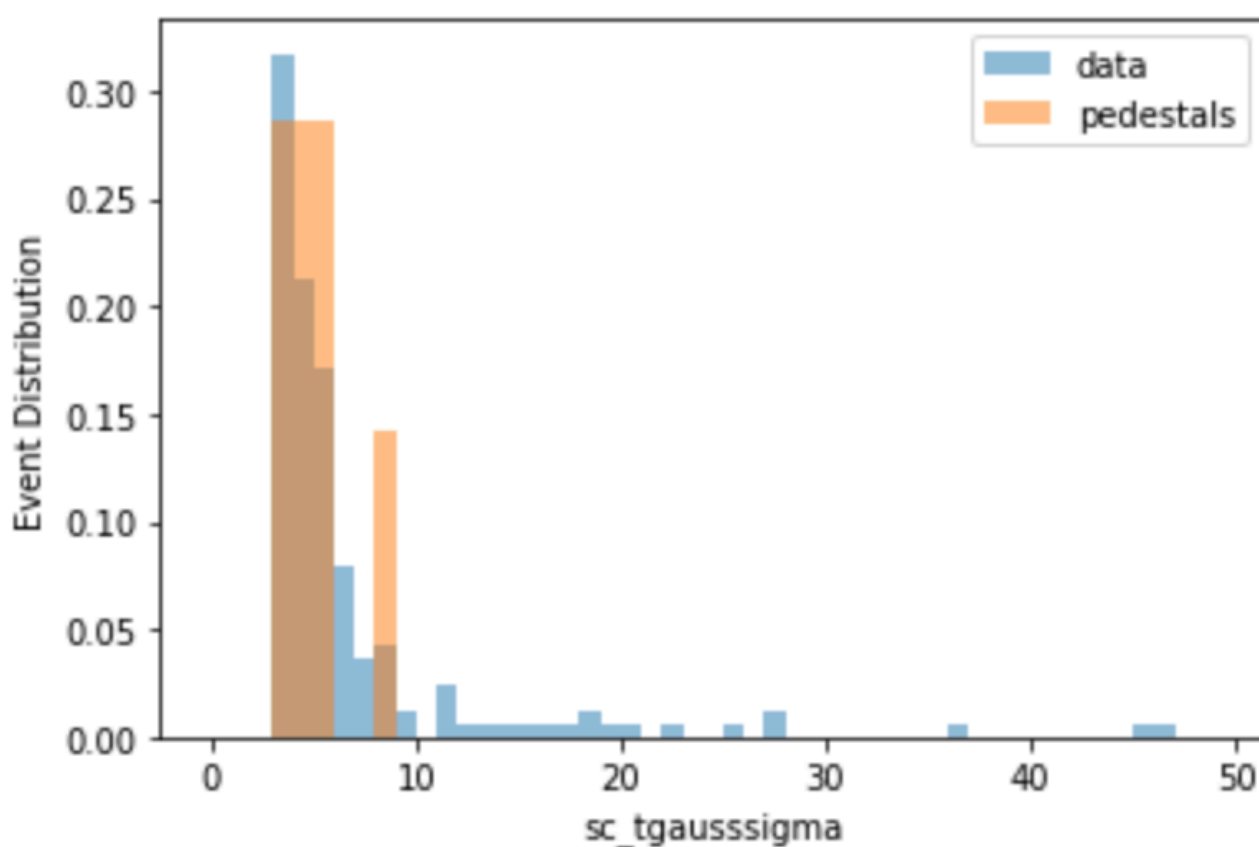
## Low Gain - Low Energy spectra

Following selection:

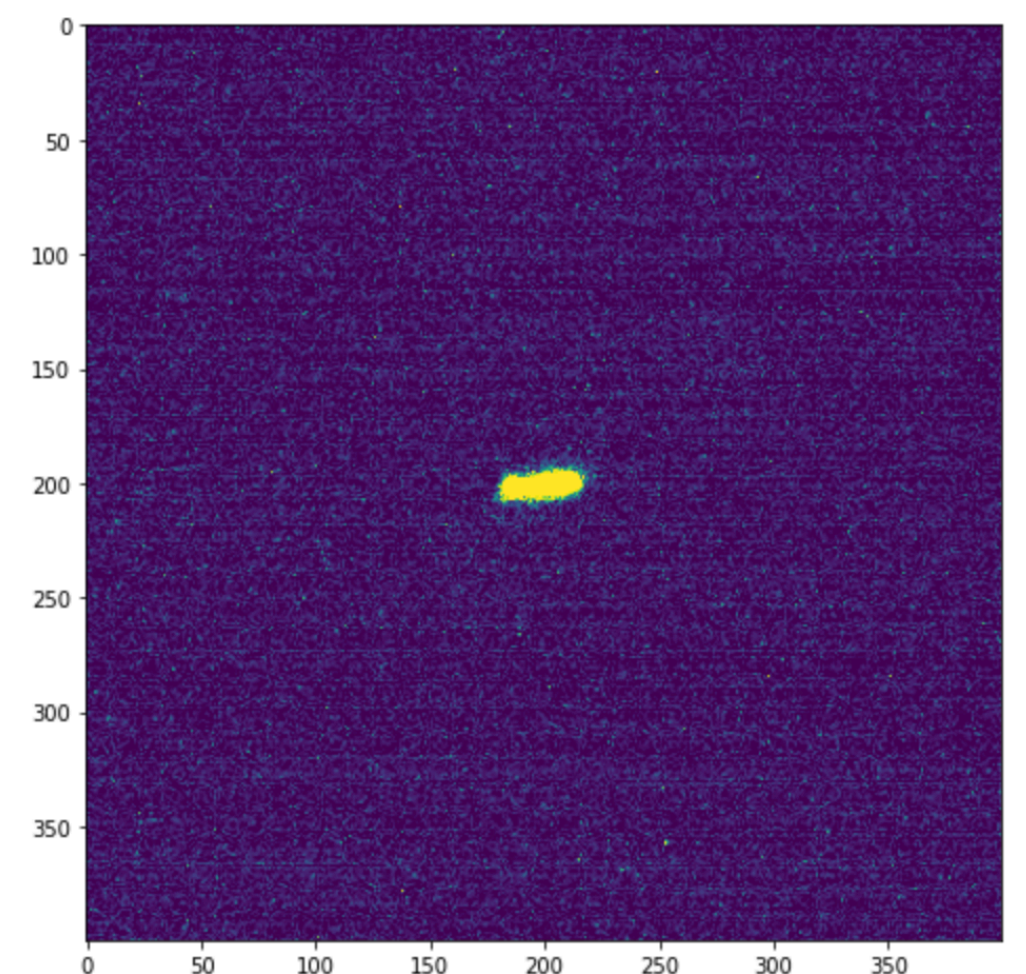
- ➡  $sc\_rms > 6$  [fake clusters]
- ➡  $sc\_tgausssigma > 0.5 / 0.152$  [events on the CMOS]
- ➡  $R < 800$  px [fiducialization]
- ➡  $sc\_integral < 50$  keVeq
- ➡  $delta > 0.023$  keVeq/pixel<sup>2</sup>



Mostly multiple hits on the CMOS clustered as a single track. How to remove them without removing interesting NR events?



Just for comparison,  
how a NR deposit looks like:  
[same pixel range]



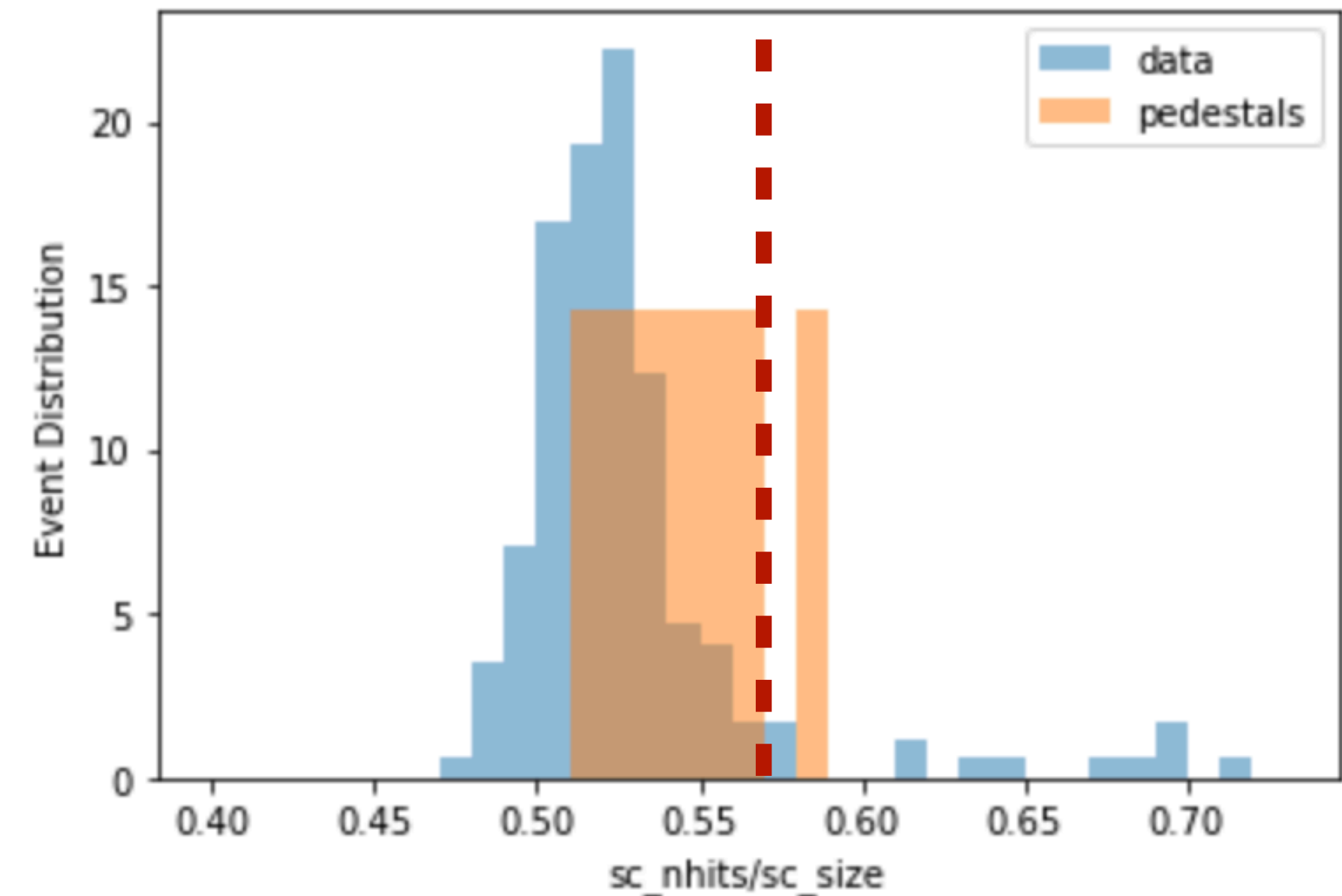


# RUN 4 - The “low” vs “high” configurations

## Low Gain - Low Energy spectra

Following selection:

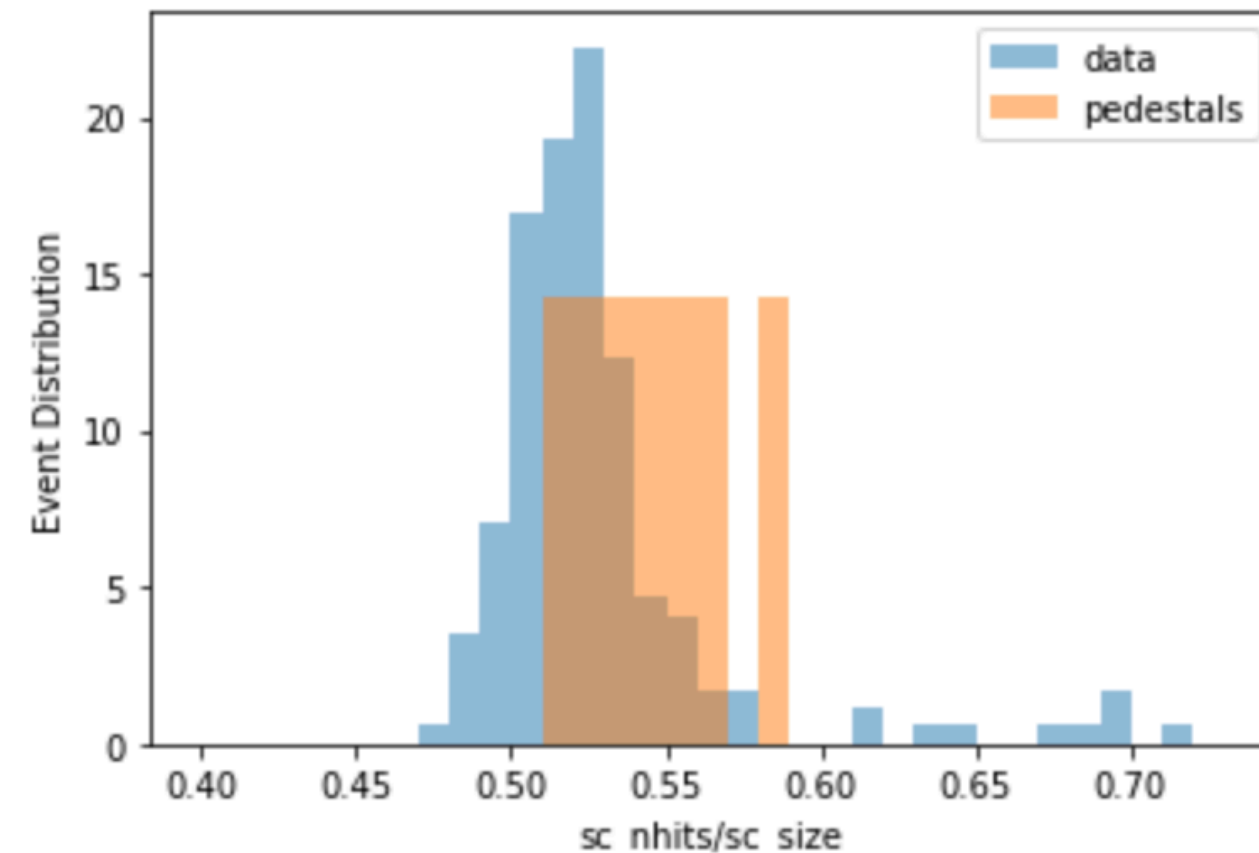
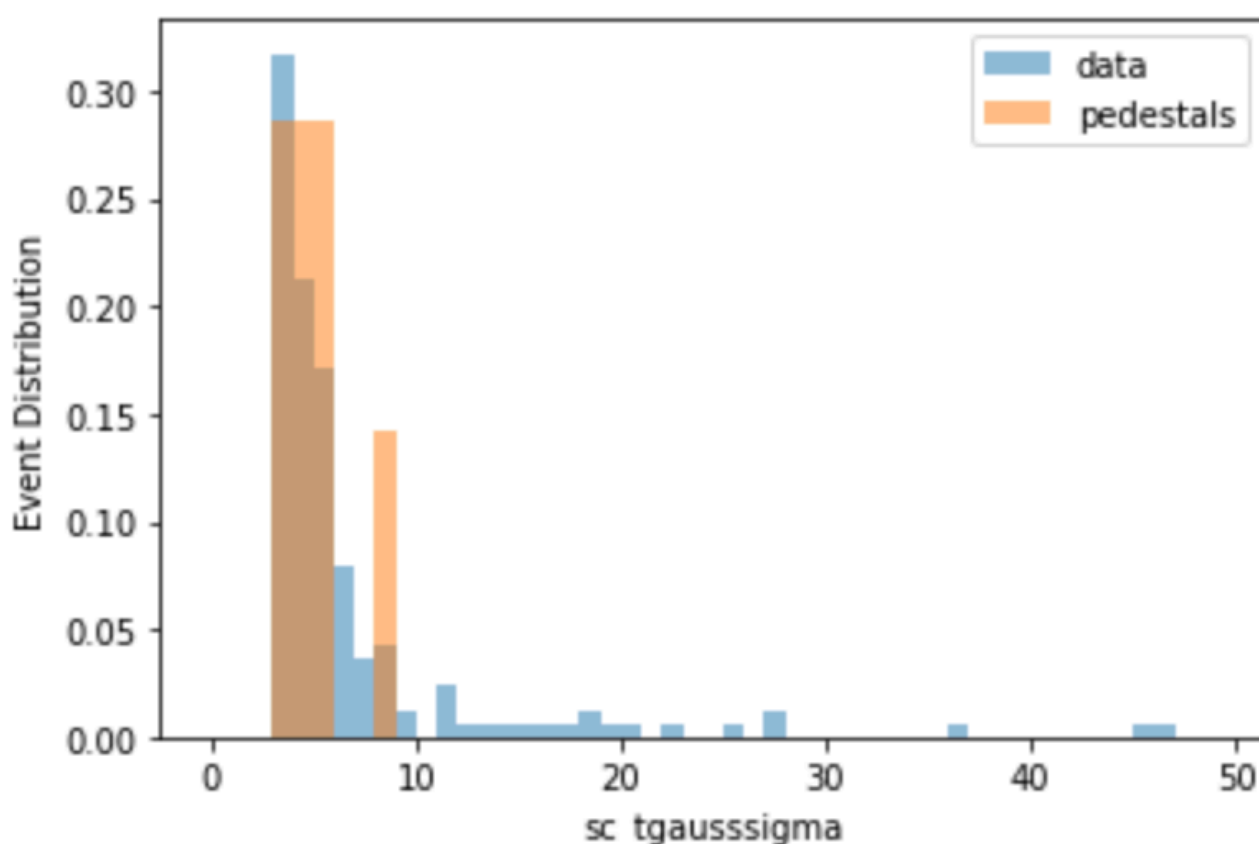
- ➡  $sc\_rms > 6$  [fake clusters]
- ➡  $sc\_tgausssigma > 0.5 / 0.152$  [events on the CMOS]
- ➡  $R < 800$  px [fiducialization]
- ➡  $sc\_integral < 50$  keVeq
- ➡  $\delta > 0.023$  keVeq/pixel<sup>2</sup>



Proposed **new cut**:

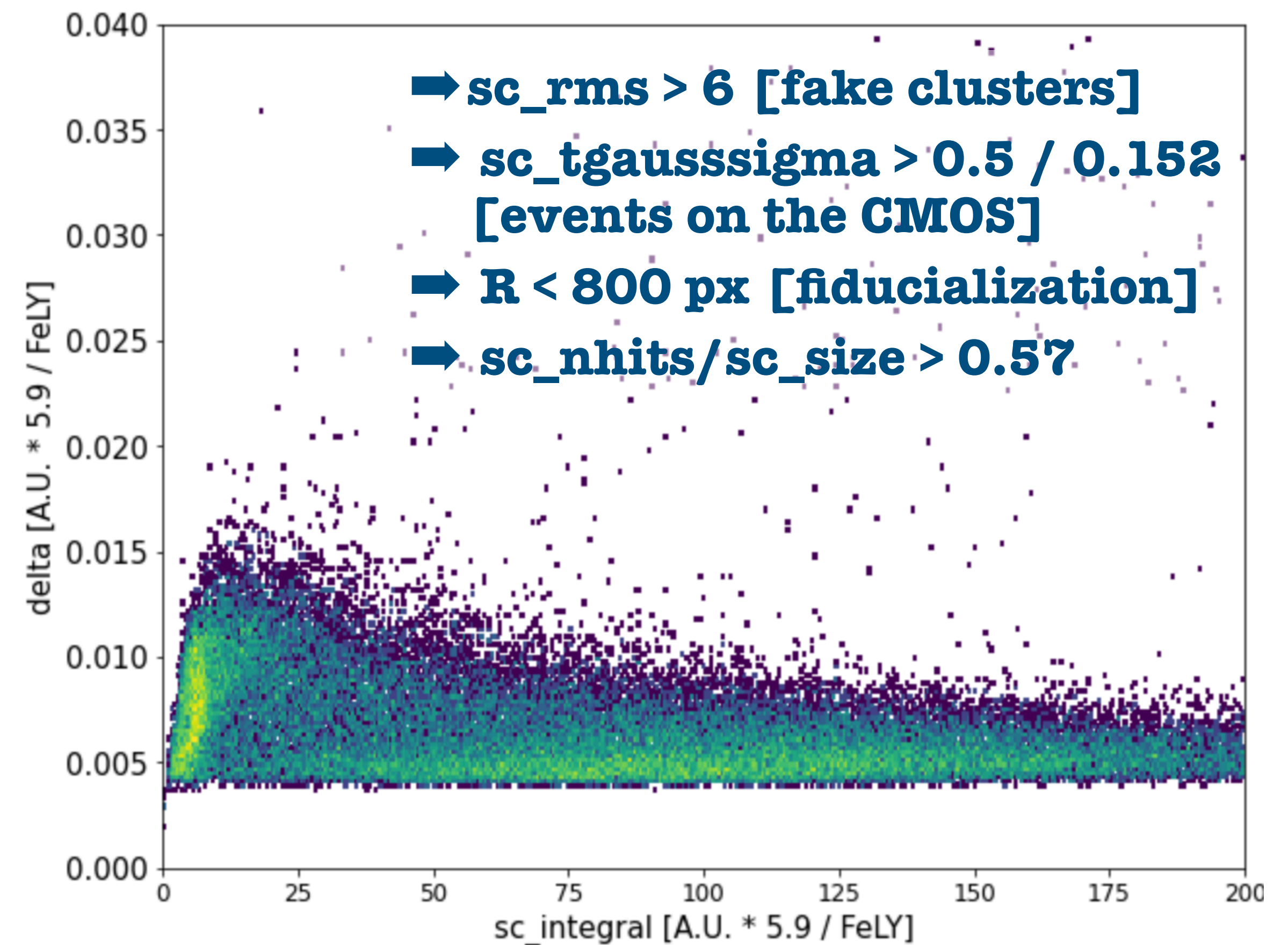
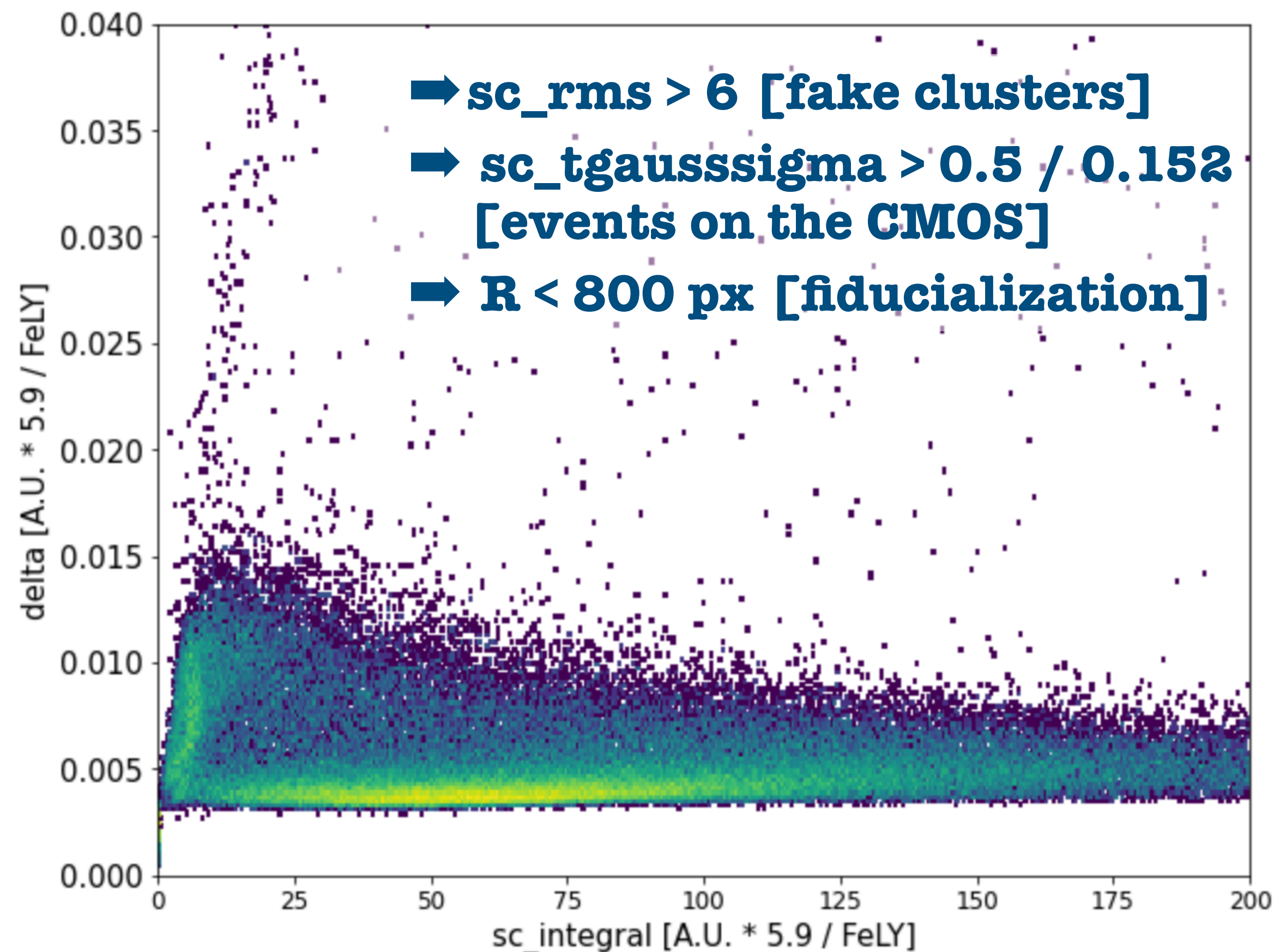
- ➡  $sc\_nhits/sc\_size > 0.57$

Equivalent to requiring 57% of pixels of the cluster above threshold. Reasonable?



# RUN 4 - The “low” vs “high” configurations

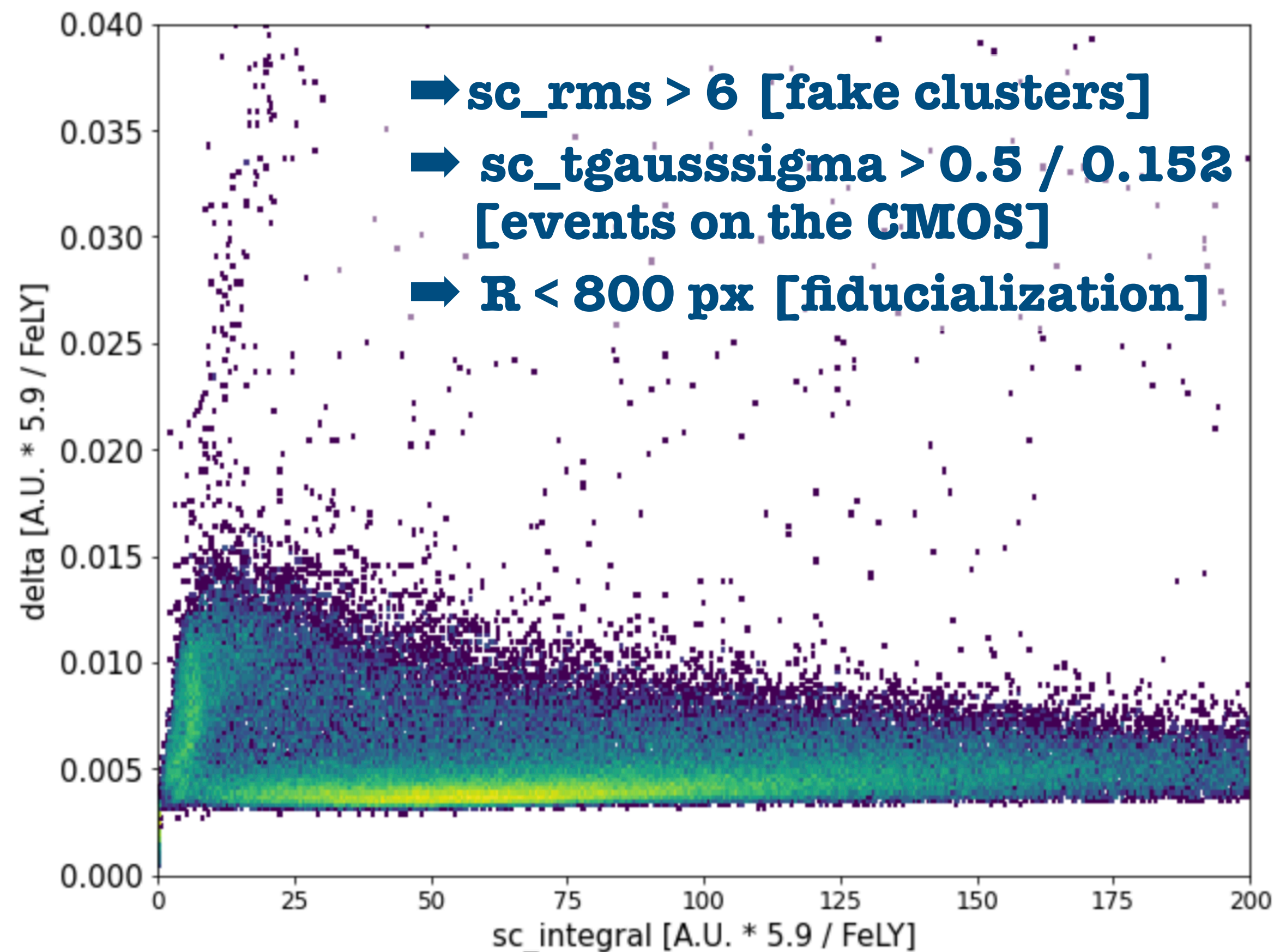
## Low Gain - Low Energy spectra



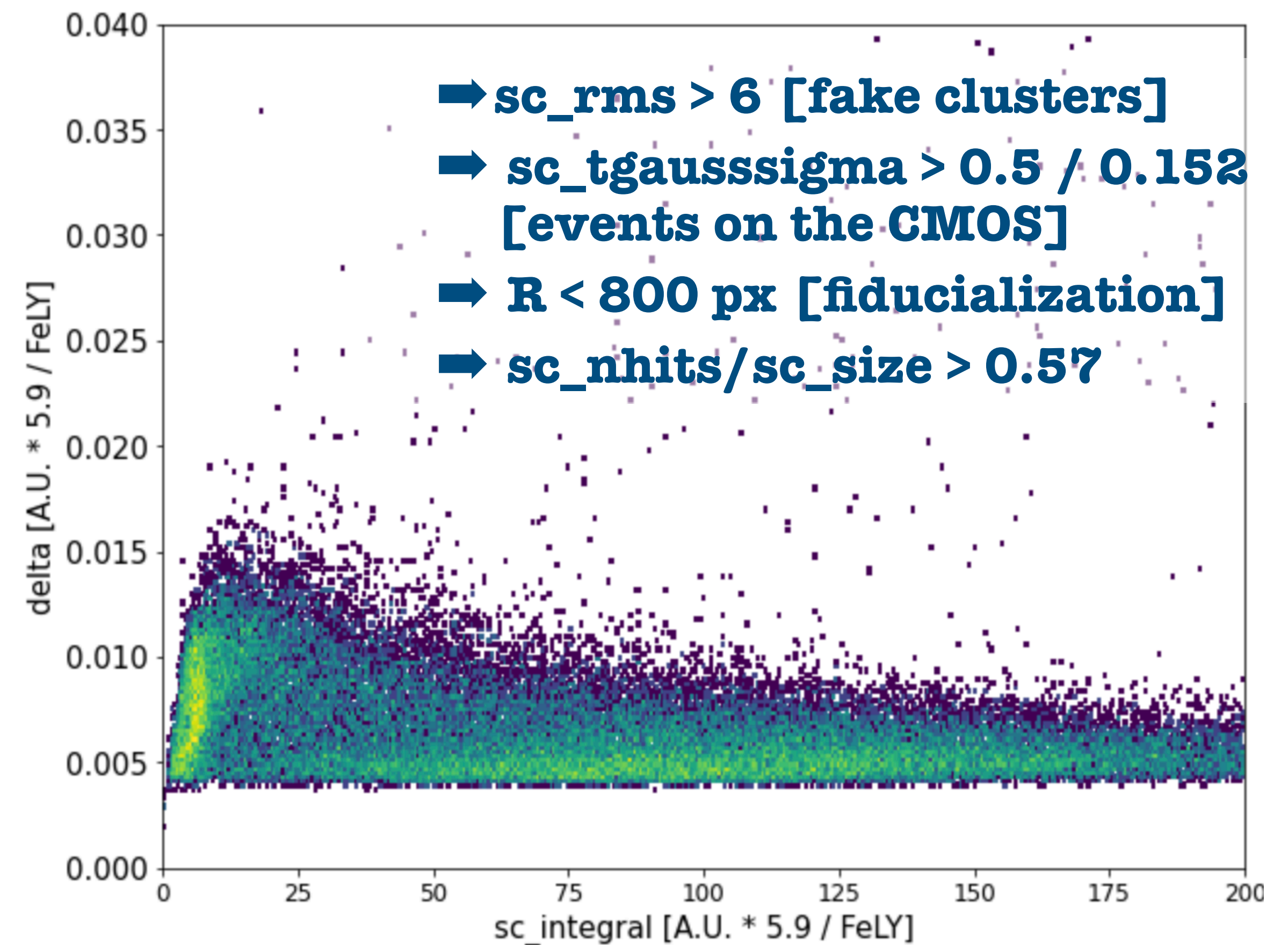


# RUN 4 - The “low” vs “high” configurations

## Low Gain - Low Energy spectra



1. The **EoS** events disappear
2. The **high density events** at **low energy** are **not influenced** by the cut
3. The **ER** band is **not influenced** by the cut
4. The **MIP** band **changes**, as expected (as it contains cut/splitted feeble tracks with a lot of sub-threshold pixels)

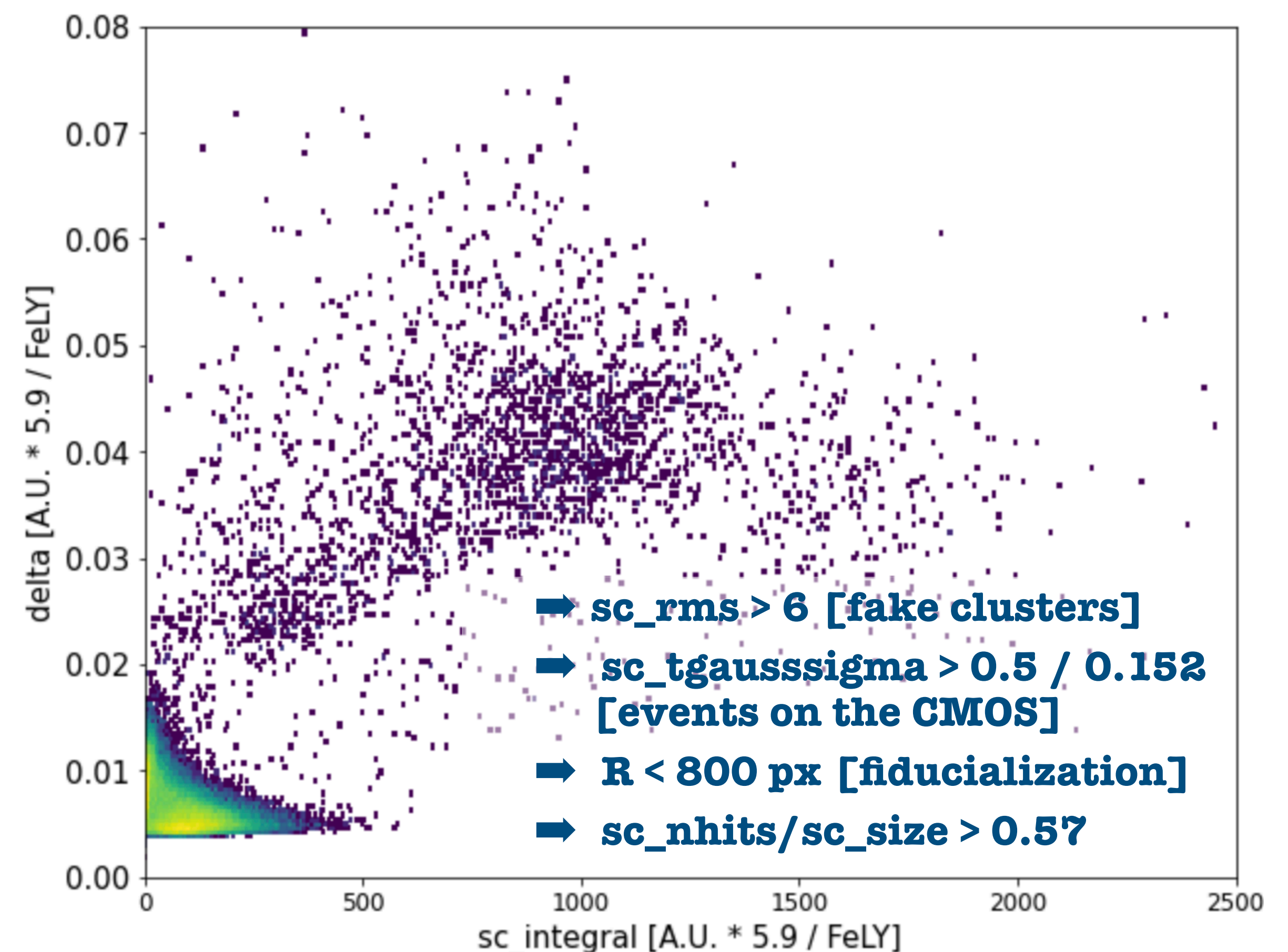
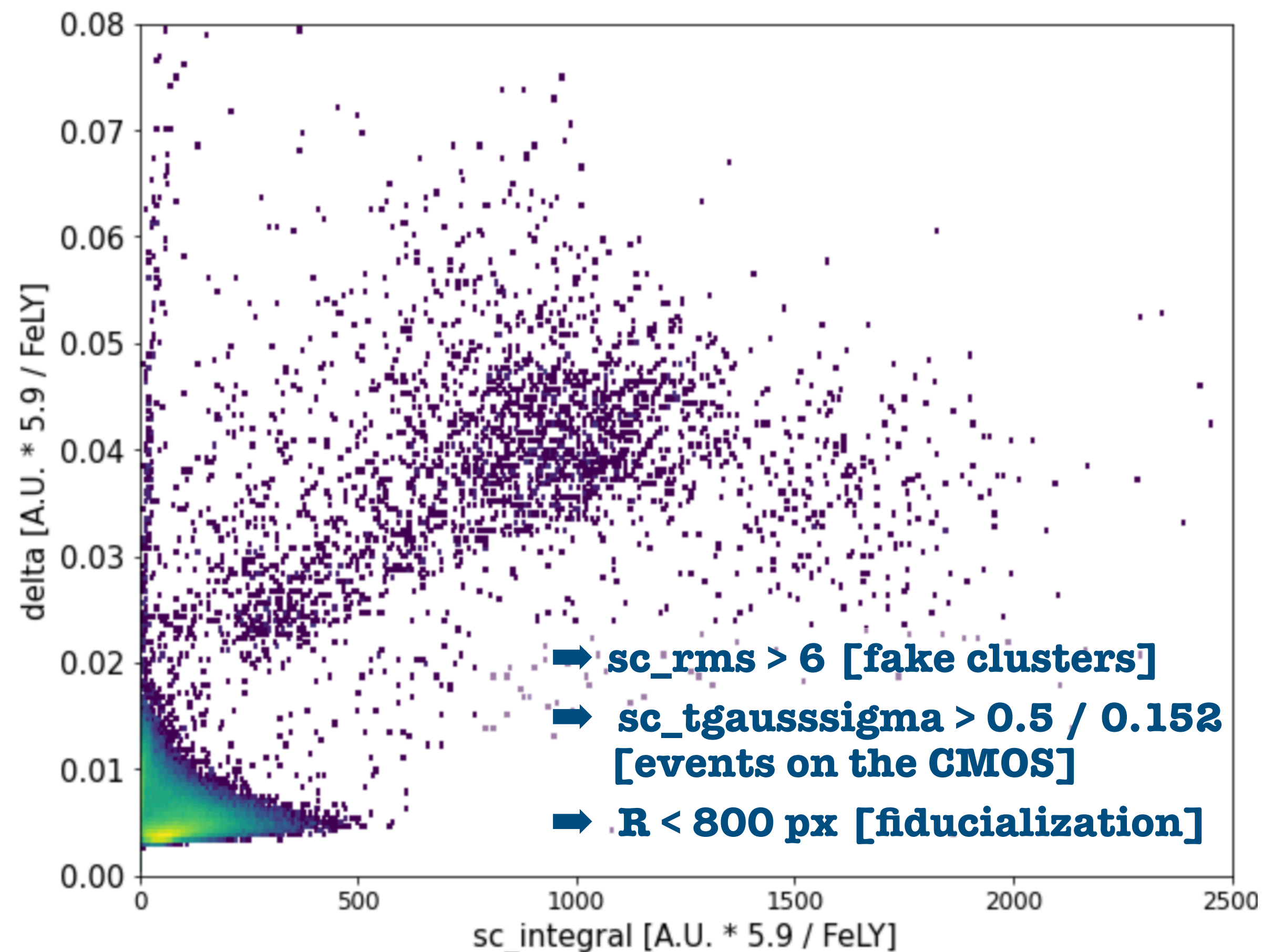




# RUN 4 - The “low” vs “high” configurations

## Low Gain - High Energy spectra

1. The **alphas seem to not be influenced**, but imho more statistics is needed to say something about the efficiency of this cut



# Conclusions

- From the point of view of the background studies, the 420 V - 500 V/cm configuration does not seem too bad wrt to the nominal configuration tested so far:
  - $>0.5\times$  in LY of the Fe spot (but not saturated)
  - +10% in the dimension of the Fe spots
- The looser reconstruction needed to deal with a lower LY introduces some issue with multiple hits on the sensor:
  - with a cut on `sc_nhits / sc_size` it seems possible to cut them out
  - this new cut seems not to affect the interesting physics (NR/alpha band and the ER band)
  - more statistics is needed for a complete study